ABSTRACT

Title of dissertation: MODELS FOR RAPID ASSESSMENT OF LEADLESS COMPONENT FAILURES DURING PRINTED WIRING BOARD BENDING Nathan John Blattau, Doctor of Philosophy, 2004

Dissertation directed by: Professor Donald Barker

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The proliferation of leadless ceramic chip components has caused their failure to become a critical issue in the electronics industry. The majority of these failures are due to mechanical loads applied to the printed wiring board during assembly. The intentions of this dissertation are to demonstrate the relationship between printed wiring board flexure and the failure of leadless ceramic chip components and to develop a methodology for rapidly assessing the risk of these types of failures. To achieve this objective, closed form structural engineering based equations have been developed for calculating the loads at the critical location within the surface mount package when the underlying printed wiring board is subjected to bending. These loads are then used to calculate the stresses in the component. Validation of these stress results was done by comparing them to those of finite element models. Failure predictions using these stresses and a probabilistic failure model were then made and compared to published experimental results. The developed methodology was then physically validated with mechanical testing and field case studies. This research identifies the physical mechanism that initiates failure in ceramic bodies attached to a glass fiber/epoxy matrix composite in a non-compliant manner, assesses the response of the mechanism to various geometries and mechanical loading conditions, and develops an analytical model that allows the user to assess risk during the design phase and to determine the root cause of field failures.

MODELS FOR RAPID ASSESSMENT OF LEADLESS COMPONENT FAILURES DURING PRINTED WIRING BOARD BENDING

By

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Dissertation submitted to the Faculty of the Graduate School of the University of Maryland, College Park in partial fulfillment of the requirements for the degree of Doctor of Philosophy 2004

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LIST OF ABBREVIATIONS

- G = shear modulus
- h = solder joint height
- δ = displacement
- ε = tensile strain
- σ = tensile stress
- y = deflection of the beam (length)
- θ = slope of the beam (radian)
- M = bending moment of beam
- E = modulus of elasticity
- I = moment of inertia (length⁴)
- v = Poisson's ratio
- L = length of beam (length)

CHAPTER 1 INTRODUCTION

1.1 Research scope and objectives

The purpose of this dissertation is to evaluate the response of the leadless surface mount structure and its interaction with the printed wiring board during a bending event. Evaluating the response provides the stresses or strains that determine when the component structure will fail by overstress. To achieve this objective, this dissertation concentrates on analytical stress model development and the corresponding failure models. The output of the analysis will be the maximum stress and the probability of failure of a component, for a given applied printed wiring board moment. The models are developed and implemented so that a rapid analysis can be conducted.

As time to market and costs are forced to decrease, the ability to conduct complex analyses is greatly reduced and many companies are unwilling to invest the money or time necessary to conduct them. However, not doing anything can incur significant costs if problems occur. Rapid assessment of component durability will provide an inexpensive alternative. The following steps were taken to develop the rapid assessment model:

- 1. Develop a general analytical method to identify the forces and moments in the component due to the effects of printed wiring board bending.
- 2. Develop a methodology for converting these loads into the stresses present in the component
- Determine the difference in values obtained from complex finite element analyses to values from the rapid closed form analytical equations

- 4. To provide parametric studies to determine the effect and relative severity of several parameters.
- Predict the overstress limit for a component under a bending event and to compare the values obtained in the analytical methodology to experimental and field results.

1.2 Motivation

Component failure due to the application of mechanical loads during board bending has become a critical issue in the electronics industry and is being driven by current and future trends in circuit design. The primary reason has been the proliferation of leadless ceramic components. As the demand for more complex and denser electronics increases, manufactures are forced to use small surface mount devices. Leaded components provide too large a footprint and cannot meet the input/output demands of most designs. These leads, which once served to facilitate manufacturing and accommodate thermally induced mismatches, are no longer present, yielding a much stiffer assembly. This added component stiffness has shifted some of the focus from thermo-mechanical induced degradation to failures of leadless devices due to pure mechanical loading or printed wiring board bending. The most common surface mount components are ceramic leadless capacitors and resistors.

A typical cell phone can contain upward to 1000 surface mount components, with twenty times more surface mount passives (capacitors, resistors, etc...) than active components

[3]. Of the capacitors used, the multilayer leadless ceramic chip capacitor (MLCC) is by far the most common, as shown Figure 1-1.



Figure 1-1: Capacitor types used in electronics [4]

The presence of such a large number of these components makes the reliability of most assemblies highly dependent on these devices. To better understand the influence of surface mount passives on failures in electronics, a review of 159 failure analyses performed by CALCE Laboratory Services, was conducted. These failures, representative of over 70 companies, were grouped by failure site and the results are shown in Figure 1-2. The most common reason for these failures was the non-functionality of a component (specifically, capacitors). Further review identified the overwhelming majority of failures as MLCCs. This is not unexpected because of the commonality of MLCCs, as displayed in Figure 1-1.



Figure 1-2: Field failure occurrences by failure site [1]

Failure studies of these ceramic capacitors were further broken down by root cause, or mechanism, by which the failures occurred. As shown in Figure 1-3, the majority of the failures were attributed to capacitor manufacturing defects. However, the second most common, which accounted for 25% of the failures, was cracking of the ceramic capacitor due to excessive flexure (or bending) of the printed wiring board. According to these results, the most common capacitor failures influenced by the designer or assembler were attributed to printed wiring board bending.



Figure 1-3: Failure mechanisms in MLCCs [1]

1.3 Background

A schematic of a typical surface mount passive is shown in Figure 1-4. The assembly consists of a leadless component on top of a printed wiring board with a solder joint attaching the component to the metallization on the board.



Figure 1-4: A surface mount ceramic chip component

Accurate failure assessments require a fundamental understanding of the architecture and materials of this structure, which includes the leadless ceramic component (capacitor and resistor), the printed wiring substrate, and the interconnect (solder).

1.3.1 <u>Multilayer ceramic chip capacitor</u>

A typical multilayer ceramic chip capacitor (MLCC) is shown in Figure 1-5.



Figure 1-5: Multilayer Ceramic Chip Capacitor

The most common MLCCs are constructed of alternating layers of $BaTiO_3$ dielectric and metal electrodes. The internal electrodes come to the surface at the face ends of the ceramic block where an electrical contact is made to the end metal termination.

There are two general types of MLCCs based upon the metals used in their construction. The traditional noble metal electrode (NME) capacitor utilizes palladium-silver (AgPd) or palladium (Pd) for its inner electrodes. The more recent and rapidly accepted base metal electrode (BME) uses nickel (Ni) or copper (Cu) for its electrodes [5.b]. Other differences in the construction in the MLCC types are detailed in Figure 1-6.



Figure 1-6: Detailed ceramic capacitor construction [5]

There are different categories of dielectric that depend on the variation in capacitance as a function of temperature. Three of the most popular barium titanate based dielectrics are shown in Table 1.

EIA		Temperature	Barium Titanate		Typical
designation	Class	range (°C)	content (%)	Other dopants	grain size
a a b i g i a a i a i a i a i a i a i a i a i					(µm)
C0G	1	-55 to 125	10-50	TiO2,CaTiO3,	1
(NPO)				Nd2Ti2O7	
X7R (BX)	2	-55 to 125	90-98	MgO,MnO,Nb2O5,	<1.5
				CoO Rare-earth	
Y5V	2	-30 to 85	80-90	CaZrO3, BaZrO3	3-10

 Table 1: Common capacitor dielectric designations [50]

1.3.2 Surface mount ceramic chip resistor

Resistors are typically the second most numerous parts used in electrical circuits. The surface mount ceramic chip resistor is a leadless device that is composed of a ceramic substrate supporting a resistive element. The substrate is a high purity alumina with the material properties shown in Table 2. The resistive element can either be a thick film or a thin film depending on the accuracy and power dissipation required.

Physical Constant	Al ₂ O ₃ (99.8%)		
Elastic Modulus	337000 MPa [10]		
Tensile Strength	220 MPa [11]		
Bending Strength	410 MPa [11]		
Coefficient of Thermal Expansion	7.8 x 10 ⁻⁶ 1/°C [11]		
Fracture Toughness	4.56 – 5.01 [10]		

Table 2: Physical properties of alumina ceramic

1.3.2.1 Thick film resistor

The thick film resistor uses a resistive paste that is screen printed onto the substrate and then fired. The paste is typically composed of metal oxides, glass and solvents. The resistance is varied by the composition of the paste, the amount of paste, and by limited laser trimming. This typically makes achieving high tolerances difficult (<0.5%). The basic construction of a thick film resistor is shown in Figure 1-7.



Figure 1-7: Thick film resistor [6]

1.3.2.2 Thin film resistor

The thin film resistor uses a metal film based resistive element that is deposited onto the substrate. The element is usually a nichrome (NiCr) or tantalum-nitride (TaN) film. Resistance of the film is determined by patterning, thickness and laser trimming. The resistance can also be controlled by baking the element, which increases the oxide thickness and therefore the resistance [9]. The basic construction of a thin film resistor is shown Figure 1-8.



Figure 1-8: Thin film resistor [7]

1.3.3 Printed wiring board

The printed wiring board (PWB), also known as a printed circuit board (PCB) is the substrate to which the electronic components are mounted. The most common PWB is called FR-4¹. FR-4 is composed of continuous glass fibers embedded in an epoxy resin matrix. The PWB supports the mechanical and electrical connections of the components

¹ FR stands for flame retardant

and provides a thermal path for power dissipated by the components. Two distinct configurations of connections are predominant; thru-hole and surface mount. A through hole interconnect uses a hole in the PWB through which the lead of the component is passed and then attached. A surface mount interconnect does not require a hole in the PWB and the component is attached directly to a bond pad on the surface of the PWB. This allows for closer component spacing and does not disturb conductors that may be routed underneath the component in different layers. The most popular material used to attach the component to the PWB is solder.

1.3.4 <u>Solder</u>

The most common solder used today is a eutectic combination of 63% tin and 37% lead. The melting temperature is around 183°C and tin-lead solders have good wetting characteristics and low cost. Solder is stencil printed onto the printed wiring board in a paste form. This paste is composed of the solder (in sphere form) and the flux. The flux is designed to remove organics, breakdown oxides and decreases the surface tension of the solder to insure good wetting. The material properties for 63Sn37Pb solder are shown in Appendix 10.2.1.

1.4 Literature review

The work that relates the failures of ceramics due to printed wiring board bending coincides with the acceptance of using surface mount components on organic based substrates in the mid-eighties [15]. Before this, surface mount devices were typically only used on ceramic substrates and actual failures due to bending were quite rare.

Instead most publications that evaluated cracking in capacitors tended to focus on those driven by thermal shock conditions. One of the first papers to address the structural reliability of leadless ceramic components on an organic substrate was written by Cozzolino and Ewell in 1980 [51].

The paper was the first to apply a physics of failure based approach to capacitor cracking. Critical material properties were measured through a variety of experimental techniques, including indentation to calculate fracture toughness, strain gages to measure residual strains, and ultrasonic methods to obtain elastic properties. Cozzolino also provided a basis for applying fracture mechanics through the use of finite element stress analysis and the calculation of stress intensity factors [54]. However, the paper did not directly address the relationship between substrate flexure and failures but instead focused on crack initiation and growth due to thermal shock.

Work by McKinney and Rice [17] in 1986 investigated the failure characteristics of surface mount capacitors. The study provided valuable data on the fracture behavior and mechanical properties of ceramic capacitors but did not extend the results to bending failures of capacitors on a substrate.

The paper "Cracks: The Hidden Defect" [16] written in 1988 by John Maxwell was one of the first to provide semiqualifiable guidelines to preventing capacitor failures due to substrate flexure. The study covered the morphology of cracks caused by thermal shock, pick and place, and board bending. It also provided guidelines on how components should be located on a board to minimize failures to due board bending. However, the guidelines were relatively broad, based only on a geometric interpretation of bending. This interpretation is shown in Figure 1-9. Using this approach, Maxwell recommends that the minimum board radius of curvature should be greater than 60 inches to avoid flex cracking. The source of this recommendation was not provided.



Figure 1-9: Geometric interpretation of board bending [16]

Work done by Condra [23] in 1992 addressed the failures of ceramic chip capacitors on alumina substrates. Environmental issues such as vibration and thermal cycling were investigated as a possible cause of capacitor cracking. The study was limited to fractional factorial experimental testing that investigated the effects of various parameters on capacitor failures. These parameters included manufacturer, soldering technique, and conformal coating, as well as temperature, humidity and vibration. The testing indicated that vibration when combined with temperature cycling could increase the number of failed ceramic capacitors. However, due to the lack of failure analysis, cracking as the root cause of these failures could not be confirmed. In regards to flex cracking, no

guidelines were suggested, though the work did indicate that rework of the capacitors could greatly influence failure rates.

The next major study involving capacitor cracking was conducted by Prymak and Bergenthal of Kemet Electronics in 1995 [21]. They conducted numerous 3 point bend test experiments on ceramic capacitors and provided a statistical analysis of the results. The report contains data on the behavior of the capacitors during flex testing and the probability of failure for two sizes of capacitors, 0805 and 1206, on a 1.6 mm thick printed wiring board. This effort resulted in the first rudimentary attempt at a failure model, with the authors providing a probability of failure due to flex cracking as a function of displacement.

Panchwagh and McCluskey [22] investigated the internal stresses generated in ceramic capacitors during wave soldering. Using finite element analysis they investigated the effects of capacitor dimensions on the capacitor stresses incurred during wave soldering. The research did not extend into flexural cracking of the capacitors.

One of the first papers that focused on predicting component failures due to substrate bending using numerical modeling was written by Franken et al [18]. The study covered a series of experiments and the attempts to model the failure behavior using finite element analysis. The report contains data on the materials and properties that make up a ceramic capacitor, the effect that increased solder joint thickness has on the failure probability of the capacitor during bending and the potential effects that residual stresses can have on the failure probability. Example, the authors did not correlate any other parameters to the failure probability of the device.

Literature on the behavior of ceramic surface mount resistors during printed wiring board bending does not seem to exist. Searches using INSPEC, IEEE Xplore and FirstSearch did not yield any articles with regards to mechanical failures of resistors. This is not surprising, due to their mechanical makeup, since the ceramic used in resistors has higher fracture strength than the ceramic used in capacitors. Therefore, more severe bending events are required for crack initiation. In addition, the functional aspect of the resistors is typically located on the top of the component, as opposed to the interior of the component, as with ceramic capacitors. With the classic morphology of flex cracks, this effectively removes the functional area of the component away from the crack path. Resistors with cracked substrates can be fully functional, unless the crack fully propagates through to the top of the device.

1.5 Industry response

1.5.1 Capacitors

Many ceramic capacitor manufacturers recognize the potential of failing ceramic capacitors when the printed wiring board is subjected to bending. The response from industry has involved numerous manufacturer publications to address the problem. Included in these papers are general guidelines with regard to placement and orientation of the capacitors on the board to minimize the potential of bending failures. There has also been industry sponsored standards developed to provide guidelines on how to assess the robustness of capacitors during board flex events. The tests involve soldering a capacitor to a 90 mm x 40 mm x 1.6 mm thick FR-4 test coupon. The coupon is then subjected to a three point bend test as shown in Figure 1-10.



Figure 1-10: EIA-J RC 3402 [22]

This is a qualification type test and the board is deflected to the desired level and the capacitor is tested while the board is in the bent state. Passing of the test is accomplished if there are no visible cracks and the capacitance has not varied by more than a specified amount (classification dependent). Some standards for the test method are:

- 1. AEC-Q200, Automotive Electronics Council (2 mm deflection)
- 2. EIA-198D / PN-2271 (United States) (2 mm deflection)
- 3. IEC 384-10 4.35 (Europe)
- 4. EIA-J RC 3402 (Japan)

Unless noted, the tests do not specify the deflection of the device. This is left up to each manufacturer. Most manufacturers usually specify that their components can pass either a 1 mm or a 2 mm deflection limit. Some major manufacturers and their deflection limits are shown in Table 3. Manufacturers not listed do not publish a deflection limit.

	E	Deflection Specifica	tion
Manufacturer	1 mm	2 mm	Other
AVX [30]		Х	X ²
Vishay [32]	X		
SAHA/Susco Components [26]		Х	
Cal-Chip Electronics, Inc. [27]		Х	
TDK [25]		Х	
EPCOS [5]		Х	
Kemet [34]		Х	
MuRata [31]	X ³		
Nippon Chemi-Con [28]	X ⁴		
Samsung Electro-Mechanics [29]	Х		

 Table 3: Manufacturer deflection specifications

² AVX offers a soft-termination capacitor with a deflection limit of 5 mm

³ GRM03, GRM15 capacitors, PWB thickness 0.8 mm

⁴ Printed wiring board thickness 1.0 mm (1.6 is the standard)

Syfer, Novacap [43]		X	X ⁵
Johanson Dielectrics [43]	X^6		X ⁷
Panasonic [39]	Х		
Philips, Phycomp, now Yageo [36]	Х		
KOA Speer Electronics [35]		Х	
Maruwa America [37]		X	X ⁸
Taiyo Yuden [38]	Х		
Walsin Technology Corp. [39]	Х		

1.5.2 <u>Resistors</u>

The electronics industry has developed standards to verify the robustness of surface mount resistors. The common test for surface mount resistors is JIS-C-5202, Para.6.1.4 [42]. The test setup is identical to that shown in Figure 1-10 except that the specified deflection is 5 mm and the ram radius is 240 mm. The ram radius is decreased to allow for greater deflections to be applied to the board.

⁵ Syfer offers a polymer-termination capacitor with a deflection limit of 5 mm

⁶ NPO class dielectrics

⁷ X7R, Deflection specification 0.5 mm on FR-4

⁸ Flexion termination, 8 mm deflection

1.6 Summary

A method for predicting the failure of ceramic chip capacitors and ceramic chip resistors is clearly needed. The number of failures of these devices is high when compared to other component level failures. Manufacturers have provided basic placement guidelines that may be used to minimize flex cracking. They have also typically provided the deflection limit at which their product can be safely used. This deflection limit may be a useful metric for comparing manufacturers, but it does not provide a designer with information on the flexure that the capacitor can survive in his application. Very few manufacturers publish the actual failure data and they also do not adequately address the effects of geometric parameters, such as board thicknesses, on the failures during printed wiring board bending.

The purpose of this study is to develop an analytical model to predict the failures of ceramic chip capacitors and resistors when they are subjected to a printed wiring board event. The analytical model can provide a rapid method by which:

- 1. The robustness of the an electronic design can be assessed with regard to the mechanical failures of resistors and capacitors
- Root cause of failures can be conclusively identified based upon printed wiring board strain readings
CHAPTER 2 LEADLESS CHIP DEVICE STRESS MODELS

In this chapter, an analytical model is developed to predict the stresses developed in leadless ceramic chip capacitors and resistors (LCC/LCR) during board flexure. The model will convert printed wiring board deformation into the forces applied to the part. Thus, the purposes of this chapter are:

- (1) To derive an analytical method for characterization of the forces and moments in terms of the geometric, material, and load parameters of the PWB
- (2) To determine the maximum loads and stresses within the leadless chip device

2.1 Analytical stress model for ceramic chip capacitors and resistors

A structural engineering approach is used to develop the analytical model for determining the stresses in the device. As shown in Figure 1-5, Figure 1-7 and Figure 1-8 the structures of surface mount resistors and capacitors are similar. Therefore, one analytical stress model should be able to predict the stresses for either device. However, some simplification of the structure is necessary for modeling. This is shown in a two dimensional representation of the device in Figure 2-1.



Figure 2-1: 2D representation of LCC/LCR structure

2.1.1 Assumptions

There are some necessary assumptions that must be made in order to reduce the structure to the point that an analytical model can be developed. The component body is assumed to be homogenous. The printed wiring board will have effective properties based upon the number and location of full internal layers (voltage/ground planes). These calculations are based upon weighted averaging and the parallel axis theorem [74]. The stack up of the printed wiring board is assumed to be symmetric. an example of a board stack-up is shown in Figure 2-2. Therefore, the centroid of the pwb will always be assumed to be one half the thickness of the board.



4 Layer

Figure 2-2: Example board stack-up

The initial assumption was that the members of the complete structure (component, solder, board) could be represented as beam type elements. This may introduce some error in the results as the elements are relatively short and their behavior may not be accurately predicted with simple beam equations because of excessive shear deformations. The accuracy can be increased by accounting for the shear, which is typically ignored in beams. The analytical stress model will also assume that the solder joint intersects the capacitor in the center of the capacitor termination (bandwidth⁹), which in this case reduces the capacitor length by 50% of the end metal termination. Furthermore, a 2-D planar representation is also assumed. This will cause some error to be introduced because any edge effects between the board and component will be

⁹ This is the length of the end metallization of the device

ignored. The amount of the error and necessary calibration factors will be determined using a finite element models. The geometric parameters shown in Figure 2-3 will be incorporated into the analytical model.



 t_c – thickness of the device

- t_{tm} thickness of the device end metallization
- t_{sj} solder joint thickness
- t_{tm} copper bond pad thickness
- t_{cu} thickness of the printed wiring board
- t_w width of the device
- l_{ps} bond pad separation
- l_c length of the device
- $l_{pad}-bond \ pad \ length$

Figure 2-3: Geometric parameters for analytical model

Additionally, the model should account for the shape of the solder fillet. There are three general classifications of the solder joint, as shown in Table 4.



Table 4: Solder joint shape classifications

The main difference in the joints is the height at the end of the component. The starved joint will have this height assumed to be half the component thickness. The nominal joint will have this height set as 0.7 times the component thickness. The bulbous joint will have the height set as 1.0 times the component thickness. These three heights will be used to calculate a change in solder area that reflects the different stiffness of each type of joint.

2.1.2 Stress analysis technique, stiffness method

Based upon the assumptions, detailed previously, and the free body diagram in Figure 2-4, which indicates that the structure is over constrained and indeterminate, an appropriate analysis was chosen.



Figure 2-4: Free Body Diagram

Many methods are available for solving such structures, most of which are variations of the stiffness method or displacement method. The stiffness method is well documented and is also known as the Finite Element Method. The stiffness method utilizes these basic steps [75]:

- Partitioning the structure into a series of discrete elements
- Formulating the stiffness matrix for each element
- Assembling the global matrix from the local stiffness matrices
- Applying the boundary conditions to obtain the reduced stiffness matrix

- Inverting the reduced stiffness matrix
- Multiplying this matrix with the force matrix to get the displacements of the nodes
- Post-processing to obtain the stresses and strains of each element

2.1.3 Stiffness method, Model development

The following example was used to demonstrate the development of the analytical stress model to predict LCC/LCR bending overstress failures. This example is of a 1206 size device that is soldered to an FR-4 printed wiring board with the parameters shown in Figure 2-5 and Table 5. The matrices and equations used can be found in Appendix 10.5.



 $t_c - 0.68 \text{ mm}$ (thickness of the device)

 $t_{tm} - 0.010 \text{ mm}$ (thickness of the device end metallization)

 t_{sj} – 0.065 mm (solder joint thickness)

 $t_{tm} - 0.035 \text{ mm}$ (copper bond pad thickness)

 t_{cu} – 1.575 mm (thickness of the printed wiring board)

 $t_w - 1.524 \text{ mm}$ (width of the device)

 l_{ps} – 1.024 mm (bond pad separation)

 $l_c - 1.524 \text{ mm}$ (length of the device) $l_{pad} - 2.024 \text{ mm}$ (bond pad length)

Solder joint type - nominal

Figure 2-5: Example structure

Material	Description	E (GPa)	
Ceramic X7R	Capacitor Body	110[18]	
FR-4	Board	17 [Appendix 10.2.2]	
Solder PbSn	Attachment	26 [47]	
Tin/Copper	End metallization	100 [18]	
Copper	Bond pad	120 [18]	

Table 5: Material properties

2.1.4 <u>Model performance</u>

The analytical model was then exercised to characterize its behavior and performance for different sized devices. The first device investigated is a 0805 size ceramic capacitor. The study involves plotting the stress output of the model as various geometric parameters of the device were changed. The first parameter modified is the capacitor thickness, which was varied between 0.5 and 1.5 mm. The results of the model with an applied moment of 100 N·mm are shown Figure 2-6.



Figure 2-6: Capacitor tensile stress as a function of capacitor thickness

As shown in the graph, the model exhibits an unusual behavior over a specific range of device thickness. This behavior is inconsistent with FEA analyses conducted in a previous study of the same geometry [2]. The problem is that the stiffness of the device is calculated with beam equations and is therefore overly sensitive to any change in thickness, as the inertia increases as a cube of the thickness. Thus, the model required reformulation to more accurately reflect the behavior of the structure.

2.1.5 <u>Reformulation of analytical model</u>

The model was reformulated to ignore the bending stiffness of the component and attach. This assumption was made from observations from previous FEA models showing that the reaction moment on the component was quite small when compared to the moment generated by the reaction forces in the structure. As shown in Figure 2-7 the component and interconnect are now replaced with spring elements. The component interconnect is modeled as a rigid bar with a series of springs. The rigid bar provides an offset so that the component and interconnect have an apparent bending stiffness.



Figure 2-7: Model representation

The analytical model is effectively reduced and simple cantilever beam equations are used to calculate the behavior of the structure. The leadless device is assumed to only supply additional rotational stiffness to the printed wiring board at the end of the device. The stiffnesses that need to be calculated are those of the printed wiring board, device body, copper bond pad, solder joint, and device metallization. The stiffness for the substrate is based upon the rotational stiffness of a cantilever beam, and is the amount of moment required to rotate the beam 1 radian. The equation for the rotational stiffness of a cantilever beam under pure bending is shown in Equation 2-1.

$$K_{\theta} = \frac{EI}{L}$$

Equation 2-1: Bending stiffness of a cantilever under pure bending

Where E is the modulus, I is the moment of inertia and L is the length. The stiffness of the copper bond pad, solder joint, and device metallization are assumed to be under pure shear with a stiffness calculated by Equation 2-2.

$$K_{S} = \frac{AG}{t}$$

Equation 2-2: Shear stiffness

Where A is the cross-sectional area, G is the shear modulus, and t is the thickness.

The stiffness of the device is assumed to be in pure tension with a stiffness calculated by Equation 2-3.

$$K_{C} = \frac{AE}{L}$$

Equation 2-3: Tensile stiffness

This results in four stiffnesses that must be combined as springs in series, as shown in Equation 2-4.

$$K_{CS} = \frac{1}{\frac{1}{K_{C1}} + \frac{1}{K_{S1}} + \frac{1}{K_{S2}} + \frac{1}{K_{S3}}}$$

Equation 2-4: Combining series stiffnesses

These combined stiffnesses must now be converted to an apparent rotational stiffness at the end of the printed wiring board. This is done by determining the moment required to rotate the rigid bar one radian. This rotation must be related to the axial deformation of the device (component and attach). The relationship between rotation and axial deformation is given by Equation 2-5.

$$\tan(\theta) = \frac{\delta}{t}$$

Equation 2-5: Rotation - deformation relation

Where θ is the rotation, t is half the printed wiring board thickness, and δ is the axial deformation of the component. Using this relationship and the small angle

approximation, the rotational stiffness due to the axial deformation of the component is Equation 2-6.

$$K_{C\theta} = K_{CS} \cdot t^2$$

Equation 2-6: Apparent rotational stiffness

Assuming compatibility, the rotation at the end of the printed wiring board due to the applied moment is calculated by dividing the moment by the sum of K_{θ} and $K_{C\theta}$. Once the rotation is computed the axial force in the component can be computed by using Equation 2-7.

$$F = \frac{K_{C\theta} \cdot \theta}{t}$$

Equation 2-7: Axial force in the component

The axial force is then used to calculate the component stresses.

CHAPTER 3 MODEL CALIBRATION

In this section, the numerical results from the analytical stress model derived in the previous section are calibrated using Finite Element Analysis (FEA). The mechanical properties used are shown in Table 5. The inputs to the analytical model were based upon a nominal solder pad and the ranges of industry specified dimensions as shown in Table 6.

Capacitor	Length	Width	Thickness		
			Min	Nominal	Max
0805	2.01	1.27	0.50	1.00	1.27
1206	3.05	1.52	0.68	1.00	1.52
1812	4.57	3.05	0.90	1.50	1.85

Table 6: Typical capacitor types and dimensions [5,18,25,26,27,28,29,30]

The analytical stress model is calibrated using a 0805 device and will then be validated for a range of device sizes in the next section. However, before conducting a finite element analysis, a convergence study was conducted to determine the optimum element size.

3.1 Convergence study

One of the reasons for conducting a convergence study was to determine the largest element that could be used in a model that would still provide the desired accuracy. This was done mainly to reduce the computational requirements of the model. As a general statement, today's computers far exceed the computational capabilities of computers just a couple of years ago and the need for conducting convergence studies has been reduced. However, they are still important in determining element size and should be conducted when doing a rigorous finite element study. The FEA model used for the convergence study was a 1.0 mm thick, 0805 size leadless device as shown in Figure 3-1.



Figure 3-1: FEA, device model: 1.00 mm thick

The mesh density was increased until the average stress values over the area of interest reached an asymptotic value. The region of interest is defined as the failure site. This

region is located where the end metallization terminates, as shown in Figure 3-2. A rectangular area of 0.02 mm^2 is taken around this region for the stress averaging.



Figure 3-2: Region of interest for convergence study

Seven finite element analyses were conducted with consecutively smaller elements. The average stress in the convergence region as a function of element area is shown in Figure 3-3. The average stress decreased as the elements got smaller. This is expected as the smaller elements increase the compliance of the model. As the element area of decreased from 0.00111 mm² to 0.000625 mm² the changes in stress values decreased from 0.1% to less than 0.007%. Therefore convergence to less than 0.01% was determined to correlate with an element area of 0.000625 mm² and 32 elements in the convergence region.



Figure 3-3: Mesh convergence results

Subsequent FEA models will use elements with an area equal to or less than 0.000625 mm² in the region of interest.

3.2 Model calibration

FEA models of a 0805 device were analyzed to develop the correction factors or modifications necessary to calibrate the analytical stress model. The nominal 0805 size capacitor is shown in Figure 3-4. This model has nominal dimensions as detailed in Table 6. The analysis assumes that all materials behave elastically. There are three rigid beams used in the model. One beam is used at the end of the board so that a moment can be applied, while the other two beams supply the symmetry boundary conditions at the center of the device. The reference points for the rigid beams are designated by the x's in Figure 3-4. The deformed FEA model after application of the load is shown in Figure 3-6.



Figure 3-4: FEA model of 0805 capacitor

3.2.1 Effects of device thickness dimensions

The thickness of the capacitor in the FEA models was varied between the minimum and maximum values shown in Table 6. The maximum tensile stress for the 0805 capacitor is recorded in Table 7 at an applied moment of 100 N·mm along with the corresponding results from the analytical model. Additional thickness values were evaluated to ensure that the models did not exhibit the behavior shown in Figure 2-6.

As shown in Figure 3-5, the analytical model is over predicting the reaction force of the capacitor. However, the behavior or response of the analytical model is similar to those of the FEA model.



Figure 3-5: FEA and analytical model results

This over prediction is due to the assumption that there is a perfectly rigid joint attaching the copper bond pad to the printed wiring board. In actuality, there is compliance in the joint because the bond pad is attached to the surface of the board. This allows shear deformation of the printed wiring board surface to reduce the forces transferred to the component.



Figure 3-6: LE11 – strain, deformation magnification 5X

Capacitor	FEA	FEA	Analytical	Analytical
Thickness	Reaction Force	(MPa)	Reaction Force	(MPa)
	(N)		(N)	
0.5 mm	51.6	213	84	132.3
0.68 mm	52.1	209	87	100.5
0.75 mm	52.7	205	87.5	92
1.00 mm	53.5	187	89	70.3
1.27 mm	53.9	172	90	56

Table 7: 0805 Analytical and FEA results

This shear deformation is better shown using a 3D FEA model of a shear loaded metal pad on the surface of a printed wiring board, as shown in Figure 3-7.



Figure 3-7: 3D FEA model of pad on board (1.6 mm thick)

Dividing the reaction force of the pad by the shear displacement will give the relative shear stiffness of the pad to board interface. An approximation of the stiffness of the board surface is the solution of a rigid disk founded on a halfspace. However, this assumes that the printed wiring board is infinitely thick, and will over predict the stiffness for thinner printed wiring boards. The basic equation for the translational stiffness of a rigid disk on a halfspace [58] is:

$$K_{S} = \frac{8}{2-\nu} \cdot Gr_{u}$$

Where v is the Poisson's ratio and G is the shear modulus of the printed wiring board and r_u is the effective radius of the bond pad. This was modified by Gazetas [59] to approximate a square rigid pad.

$$K_{s} = \frac{9}{2 - \nu} \cdot Ga$$

Where the radius is replaced by "a" which is equal to half the pad side length. Five finite element models were analyzed to compare the effect of varying thicknesses on the stiffness. The stiffness was calculated by dividing the reaction force by the applied displacement. Comparison of this calculated stiffness with the 3D finite element model is shown in Table 8.

PWB Thickness	FEA - Stiffness	Calculated Stiffness
	1 = 0 + 0 = = 1 / 2	
0.8 mm	15040 N/mm ²	
1.6 mm	18030 N/mm ²	
3.2 mm	21190 N/mm ²	21980 N/mm ²
4.8 mm	22070 N/mm^2	
6.4 mm	22090 N/mm^2	
0.4 11111	22090 IN/IIIII	

 Table 8: Rigid Square on a halfspace comparison (width 1.0 mm)

As shown by the table, the FEA model stiffness approaches the calculated value as the printed wiring board gets very thick. The board becomes less stiff as the thickness decreases because less board volume is available to resist the movement of the pad. Figure 3-8 shows the stress fields generated in the printed wiring board after the pad has

translated 0.01 mm in the horizontal direction. As shown by the figure the stresses drop quite rapidly in the board thickness direction, about an order of magnitude at 0.7 mm.



Figure 3-8: Stress distribution, 0.01 displacement

The analytical model is modified to account for this by the addition of a spring offset by a rigid bar on the surface of the printed wiring board, as shown in Figure 3-9.



Figure 3-9: Modified model representation

The offset of the spring is set to one half the printed wiring board thickness. As a first order approximation, a printed wiring board surface shear stiffness that is not a related to printed wiring board thickness will be used. Modifying and rerunning the model yields the results shown in Table 9

Capacitor	FEA	FEA	Analytical	Analytical
Thickness	Reaction Force (N)	(MPa)	Reaction Force (N)	(MPa)
0.5 mm	51.6	213	58.2	91.7
0.68 mm	52.1	209	59.8	69.2
0.75 mm	52.7	205	60.2	63.2
1.00 mm	53.5	187	61.25	48.2
1.27 mm	53.9	172	61.9	38.4

Table 9: 0805 Analytical and FEA results

The analytical model results are now within 15% of the FEA results. However, the stress values predicted by the analytical model are much lower than those predicted by the finite element models.



Figure 3-10: FEA and analytical model results

As shown in Figure 3-10 a simple stress calculation, such as force divided by area, is not adequate to represent the stress distribution in the capacitor. An example of the stress variations through the thickness of the capacitor are shown in Figure 3-11. The analytical stress is calculated assuming an axial application of the force. However, the device is loaded on an edge and therefore has an eccentric loading. Modification of the stress calculation to account for this eccentric loading is therefore necessary.



Figure 3-11: Tensile stresses in the capacitor

The results from the finite element analyses are used to develop a stress concentration factor that is dependent on the thickness of the device. The maximum stress will be divided by the average stress predicted by the finite element model and then plotted as a function of device thickness. This stress concentration factor is used in the analytical model to account for the edge loading effects of the actual device. The stress concentration factor calculated from the FEA results is:

$$S_{f} = 3.18 * t + 1.2$$

The results of the analytical model compared to the FEA results for a 0805 device using the stress concentration factor are shown in Figure 3-12. The difference between the FEA and analytical model stress values are less than 5% over the range of device thicknesses.



Figure 3-12: Tensile stress comparison between FEA and analytical model

3.2.2 Effects of attach dimensions

3.2.2.1 Shape

The device attach parameters were varied to determine the analytical models sensitivity to them. Three solder joint shapes were investigated, as shown in Table 4, while the standoff height of the component was held constant. The FEA models used to validate the analytical model are shown in Table 10 along with the factor used to modify the solder dimensions in the analytical model. This factor (J_f) is a geometric interpretation of the solder joint shape and is roughly equal to the distance from the bondpad edge to the fillet meniscus and is used to modify the length of the solder joint to reflect the contribution of the fillet to the solder stiffness calculations.



Table 10: FEA Models of different joint types and J_f factors

A comparison between the analytical model and the FEA models are shown in Table 11. The results show that the analytical model agrees with the FEA results for the three fillet shapes.

Solder	FEA	FEA	Analytical	Analytical	
Shape	Reaction Force	MPa Reaction Force		МРа	
Starved	52.3	166.8	52.2	169.5	
Nominal	53.5	187	56.7	184.2	
Bulbous	57.3	203.4	61.9	201.2	

Table 11: Analytical and FEA results

The results shown in Table 11 are displayed graphically in Figure 3-13.



Figure 3-13: Analytical and FEA results

As stated previously these results are based upon the solder shapes defined in Table 4. The optimal joint shapes recommended by manufacturers vary. Many manufacturers are specifying smaller joints that would have been previously regarded as insufficient. This may be done to increase the joint compliance in an effort to minimize the potential for flex type failures.

3.2.2.2 Solder joint thickness

The FEA model was modified to investigate the effects of varying the thickness of the solder underneath the component. Four solder thicknesses representative of those seen on actual devices were studied, as shown in Table 12. The results show that the stresses in the device are not as sensitive to the solder thickness. Both the analytical model and the FEA predict the same behavior.

Solder	FEA	FEA	Analytical	Analytical
Thickness	Reaction Force (N)	(MPa)	Reaction Force (N)	(MPa)
0.0408 mm (1.6 mil)	58.8	199.5	65	211.2
0.0508 mm (2.0 mil)	58.1	201.5	64.6	209.8
0.127 mm (5 mil)	53.5	187	61.9	201.2
0.254 mm (10 mil)	51.2	175	57.9	187.9

Table 12: Analytical and FEA results



Figure 3-14: FEA and analytical model results

As shown by the figure the analytical results are within 10-15 MPa of the FEA results.

3.2.3 Effects of printed wiring board thickness

The FEA model was is used to investigate the effects of varying the thickness of the printed wiring board. Four thicknesses were studied, as shown in Table 13. The previous studies were all conducted with a load of 100 N·mm. However, in this study the load will be adjusted so that the surface strain of the printed wiring board remains a constant one percent.

The results and the applied moments are shown in Table 13. The results plotted in Figure 3-15 show that the 2D finite element model has a large dependence on the printed wiring board thickness and may not reflect the actual response of the structure. The analytical model is less sensitive to changes in the thickness under a constant surface strain. The stress values predicted by the 2D FEA for the thinner boards did not appear to be realistic, and a 3D FEA model was constructed to verify the results.

The 3D model is used to verify the 2D FEA model and to investigate the effect of the thickness of the printed wiring board on the capacitor stress. The 3D model is shown in Figure 3-16, and utilizes symmetry about the center of the capacitor. The moment is applied by connecting a rigid surface to the end of the printed wiring board.



Figure 3-15: 2D FEA and analytical model results



Figure 3-16: 3D FEA model, 3.15 thick PWB

The deformed model shown in Figure 3-17 illustrates the bending behavior and the strains of the board. A comparison of the finite element analyses and the analytical model results are displayed in Figure 3-18. It can be seen that the 2D finite element and the analytical models do not agree with the results of the 3D models. This is mainly due to changes in the joint compliance as the thickness of the board increases. The initial assumption that the board shear stiffness does not change as a function of board thickness was not accurate and will be modified accordingly.

The equation $K_s = \frac{9}{2-\nu} \cdot Ga$ is modified to include effects of the printed wiring board thickness as shown by the 3D finite element model. The modified equation for the board surface shear stiffness is:

$$K_{S} = \frac{9}{2-\nu} \cdot Ga \cdot 1.4 \cdot t^{0.5}$$

PWB	Applied Moment	2D - FEA	3D - FEA	Analytical	Adjusted
Thickness	(N.mm)	(MPa)	(MPa)	(MPa)	(MPa)
0.788 mm	22.34	37.8	114.8	115.3	121
1.57 mm	88.7	165.9	205.2	167.8	201
1.57 11111	00.7	105.7	205.2	107.0	201
2.36 mm	200.4	252.1	275.6	197.8	262
3.2 mm	368.5	305.3	337.6	218.4	315

Table 13: Analytical and FEA Results, 0.01 surface strain

As shown by Figure 3-18 the analytical model results are within 5 -6 % of the 3D finite element results.



Figure 3-17: 3D FEA model, 0.788 thick PWB, LE11 strains



Figure 3-18: FEA and analytical results
3.2.4 Effects of device length

Additional finite element models were used to compare the stresses of device of varying lengths to those predicted by the analytical model. Three lengths representative of 0805, 1206 and 1812 capacitors were investigated. The board and capacitor thicknesses were held constant and the end metallization was adjusted to reflect the dimensions shown in Table 6. The results under a constant board strain of 0.002, which is typical of strains encountered during capacitor failures, are shown in Table 14.

	Applied	3D - FEA	Analytical
Capacitor Size	Moment	MPa	MPa
	(N.mm)		
0603	10.7		33
0805	17.9	40.4	40.1
1206	21.4	52.6	50
1812	42.8	54.7	53.8
2512	42.8		57.8

Table 14: Analytical and FEA results, 0.002 surface strain

As shown by Table 14 and Figure 3-19 the analytical model agrees within 5% of the 3D FEA results so that no adjustment is necessary.



Figure 3-19: FEA and analytical results

3.3 Summary

The analytical model has been compared to a combination of 2D and 3D finite element models. Several modifications factors have been introduced and implemented.

- An additional spring to account for the surface shear stiffness of the printed wiring board. This is based upon a rigid disk on a halfspace and modified to account for varying board thicknesses
- 2. Modifier on the solder joint length to account for the effect of the fillet shape. In this case a starved solder joint (i.e. a small fillet) has the stiffness of the solder joint reduced by modifying the length of the solder joint, a bulbous solder joint has the solder length lengthened to increase the stiffness.

3. A stress concentration factor calculated from 2D finite element analyses. This is to account for the edge loading of the device

The analytical model has been shown to provide device stress values as a function of printed wiring board strain. The analytical model behaves in much of the same manner as finite element models and should be sufficient for making predictions on the failure of leadless chip devices.

CHAPTER 4 MODEL VALIDATION

The calibrated analytical stress model is validated using 3D finite element models. The primary stress drivers as identified in the calibration section are:

- 1. Device length
- 2. Solder joint shape
- 3. Printed wiring board thickness

4.1 Test matrix

A partial factorial approach was taken and the test matrix is shown in Table 15. The loading will be an applied board level strain of 2000 $\mu\epsilon$. This board level strain is more representative of those seen during printed wiring board bending events. Using this matrix means that nine FEA models must be constructed to validate the analytical stress model.

		Solder Joint Shape		
		Starved	Nominal	Bulbous
	Minimum	0805, 1812		0805, 1812
	(0.8 mm)			
PWB	Nominal		1206	
Thickness	(1.6 mm)			
	Maximum	0805, 1812		0805, 1812
	(3.2 mm)			

Table 15: Test matrix for model validation

4.2 FEA results

An example of the FEA models run is shown in Figure 4-1. The models were half symmetric about the center of the capacitor. A moment was applied to a rigid surface tied to the end of the printed wiring board that generated a surface strain of 0.002.



Figure 4-1: 3D FEA model, 1812 size device, with a starved solder joint

The results of the calibrated analytical model are shown in Table 16. As shown the analytical results vary between 85% and 112% of the FEA results. The average difference between the analytical and FEA are within 2%

Device Size	Solder Joint	PWB Thickness	3D – FEA (MPa)	Analytical (MPa)	Percent Difference
0805	Starved	0.8 mm	21.3	24.5	-15.0%
0805	Bulbous	0.8 mm	26	26	0.0%
0805	Starved	3.2 mm	63	61.3	2.7%
0805	Bulbous	3.2 mm	75.2	70	6.9%
1206	Nominal	1.6 mm	52.6	49.5	5.9%
1812	Starved	0.8 mm	28.3	30	-6.0%
1812	Bulbous	0.8 mm	33.4	31	7.2%
1812	Starved	3.2 mm	96.5	92	4.7%
1812	Bulbous	3.2 mm	113.8	101	11.2%

Table 16: Analytical and FEA results, 0.002 surface strain

As shown in Figure 4-2, the analytical model predicts stress relationships that agree with those shown by the FEA stress values. The analytical model typically provides predictions within -15% to 12% of those from FEA.



Figure 4-2: Analytical and FEA stress predictions

The analytical stress model provides results that are comparable to that of FEA. The relationships shown by the analytical model for capacitor length, printed wiring board thickness, and solder joint shape are very similar to those shown by the FEA models. The stress results should be sufficient to predict failures for these types of devices.

CHAPTER 5 LEADLESS CHIP DEVICE FAILURE MODEL

The failure behavior of leadless chip devices when subjected to printed wiring board bending are typically specific to the device type and very dependent on the materials and geometry. This dependency can be used to limit the failure mechanisms and sites for the leadless chip device. For example, multilayer ceramic chip capacitors (MLCC) are known to fail during printed wiring board bending. The failure mode is cracking of the capacitor body. Therefore, solder joint failures are not typically associated with MLCCs and do not need to be assessed in regards to failure predictions. This is not unexpected as the fracture toughness of BaTiO₃ is approximately 1 MPa·m^{1/2} resulting in a relatively low fracture strength.

There are four potential failure sites associated with bending of leadless chip devices:

- 1. Component body
- 2. Component end metallization
- 3. Solder joint
- 4. Copper bond pad

The component body can fail by cracking. The crack can intersect the resistive element or the electrodes of the component causing the resistance to increase or the capacitance to decrease. In brittle materials, the defects in the ceramic and the ceramic formulation will determine the stress at which the cracking will occur. The ceramic used for making capacitors has fracture properties that are highly dependent on the manufacturer.

5.1 Failure modes

5.1.1 Capacitors

When a capacitor fractures the resulting crack may cause failure by intersecting the electrodes. This will cause a decrease in the capacitance or short the electrodes together causing a short to occur across the capacitor. A crack that intersects the electrodes is shown in Figure 5-1.



Figure 5-1: Capacitor cracking (intersecting electrodes)

Not all cracks will cause the capacitor to fail immediately. As shown in Figure 5-2, a crack limited to the margin of the capacitor does not intersect any functional aspect of the capacitor and is therefore not detectable, but still may represent a reliability concern due to the potential for long term crack growth.



Figure 5-2: Capacitor cracking (margin only)

5.1.2 <u>Resistors</u>

The ceramic used for resistors, aluminum oxide (Al_2O_3) has a higher fracture strength and higher stresses are therefore required to initiate cracking in the component body. Actual experimental failures of leadless chip resistors indicate two failure modes.

- 1. End metallization cracking
- 2. Body cracking

As shown in Figure 5-3, an end metallization failure occurs when the metal termination of the resistor separates from the ceramic substrate. Once separated, the resistor will no longer function properly.



Figure 5-3: Resistor metallization failure [35]

Resistor body cracking is the second failure mode of ceramic resistors. A resistor body crack, as shown in Figure 5-4 may cause failure if the crack intersects the resistive element or electrically separates the resistor from the board. Both failure modes share the same crack initiation site. The main difference is the path along which the crack propagates.



Figure 5-4: Resistor body cracking

Board bending failures of the bond pad and solder joint are very rare with regard to leadless chip devices and often require the presence of severe defects in the solder or printed wiring board (i.e. voiding, poor wetting, intermetallic formation, etc..). Typically, bond pad failures occur when the solder joint has a greater area than the pad, such as the case with non-soldermask defined (NSMD) ball grid array joints [72]. Experiments indicate that even under extreme bending conditions solder joint or bond pad failures do not occur [35].

5.2 Failure models, capacitors

As stated previously, the dominant failure mode of multi-layer ceramic capacitors during printed wiring board deflection is cracking of the capacitor body. Manufacturers recognize resistance to cracking as critical measure of the durability of their capacitors and typically provide test data that reflects the capacitors durability. However, this data is extremely limited and typically only available for capacitors that are 0805 or smaller. Therefore, the applicability of a theoretical fracture mechanics failure model will be investigated and compared to an overstress based failure model derived from manufacturer test data.

5.2.1 Ceramic capacitor fracture mechanics failure model

The ceramic used in capacitors is typically a doped barium titanate (BaTiO₃). Manufacturers either formulate the ceramics themselves or acquire them from titanate vendors [50], depending on the complexity of the formulation. For example, ceramics such as Y5V are simple enough that manufacturers may formulate them in house. Large ceramic vendors such as Murata, TDK and Kyocera do this. The formulations of the ceramics are typically proprietary and can vary from manufacturer to manufacturer. This means that the strength of the ceramic may also vary depending on the manufacturer. The variation in fracture strength will be dependent on [52]:

- 1. Fracture toughness K_c
- 2. Flaw size (defects)
- 3. Residual stresses

The fracture toughness is typically dependent on the fracture mode. The three basic fracture modes are:

- I. Opening mode
- II. Sliding mode
- III. Tearing mode

The three modes of fracture are shown in Figure 5-5. The failure of brittle ceramics is typically dominated by Mode I [53]. The cracks shown in Figure 5-1 are typically associated with Mode I type fracture behavior.



Figure 5-5: Three modes of fracture

Assuming that a straight single ended crack initiates at the edge of the capacitor, Griffith [52] formulated an expression that states that the fracture stress (σ_F) is defined by the equation:

$$\sigma_{F} = \left(\frac{2YE}{\pi c}\right)^{\frac{1}{2}}$$

Where Y is the Young's modulus, E is the surface energy and c is the half length of a crack. Further experimental work by Griffith determined that there was a relationship between the flaw size and the fracture stress. Work done by Griffith was expanded by Irwin and Kies [54] who developed the concept of stress intensity factors, K (after Kies). This was developed into the well known fracture equation, for mode 1, where the fracture toughness, K_{IC} [53] is defined as:

$$K_{IC} = \frac{\sqrt{2YE}}{\pi}$$

Converting the energy to applied stress and accounting for an edge crack yields the following equation [53]:

$$K_I = 1.12\sigma_F \sqrt{\pi a}$$

Typical published values of K_{IC} of X7R ceramics are usually between 0.9 and 1.3 MPa.m^{1/2} [56]. When $K_I > K_{IC}$ then the crack will propagate through the ceramic and cause failure. Koripella [12] conducted experiments to characterize the fracture behavior of capacitor dielectrics C0G, X7R, and Z5U and reported the fracture stress, Weibull modulus and fracture toughness. The edge crack, flaw size (a) in Table 17, is computed from this data.

 Table 17: Computed flaw sizes from experimental data [12]

Dielectric	Fracture Stress	Weibull	K _{ic}	
Туре	50% Failure (MPa)	modulus	$(MPa \cdot m^{1/2})$	Flaw Size (µm)
C0G	175	4.8	1.5	18.6
X7R	166	6.5	1.03	9.8
Z5U	116	3.9	1.01	19.2

Actual identification of flaws of this size is possible. As an example, a 1206 size X7R capacitor was inspected using an environmental scanning election microscope. A low magnification image of the capacitor is shown in Figure 5-6.



Figure 5-6: ESEM image, 1206 capacitor, 159X magnification

Magnification was further increased to identify flaws of the size calculated in Table 17. The areas inspected correspond to the areas where cracks are known to initiate, as shown in Figure 5-1 and Figure 5-2. A thorough inspection of the capacitor yielded no discernible defects at a magnification of 3090X, as shown in Figure 5-7. The magnification was increased to 10119X, and the capacitor was re-inspected. At this high magnification small pore like structures, on the order of 0.5 to 1.0 µm were evident, as shown in Figure 5-8.



Figure 5-7: ESEM image, 1206 capacitor, 3090X magnification



Figure 5-8: ESEM image, 1206 capacitor, 10119X magnification

Assuming that these pores act as defects and are the initiation sites, the required fracture stress is computed and shown in Table 18. This fracture stress is around 509 MPa and is much higher than reported maximum fracture stress values for X7R type capacitors [18].

Dielectric	Fracture Stress	K _{ic}	
Туре	50% Failure (MPa)	$(MPa \cdot m^{1/2})$	Flaw Size (µm)
X7R	509	1.03	1.0

 Table 18: Computed fracture stress

It has been hypothesized that the porous nature of the interface between the end metallization and the ceramic is actually providing the crack initiation sites [30]. As shown in Figure 5-8, a fairly large gap is present between the metallization and the ceramic, which could act a crack initiation site. However, the time required to characterize the fracture properties of this interface for the various capacitor manufacturers would defeat the purpose of a rapid analysis approach. A more realistic approach would be the utilization of a failure model that recognizes that there is a distribution of flaws that generate corresponding stresses at which fracture will occur.

This was first proposed by Weibull [55], and the resultant relationship has 2-parameters, the Weibull modulus and characteristic strength. This equation can also be modified to factor in the volume of the sample to reflect the flaw population at the crack initiation site. The equation for computing the survival probability of a sample (constant size, and shape) is shown in Equation 5-1.

$$\phi = \exp\left\{-\left(\frac{\sigma}{\sigma_o}\right)^m\right\}$$

Equation 5-1: Failure distribution calculated using the Weibull modulus [53]

Where φ equals the survival probability, m is the Weibull modulus, σ is the applied stress, and σ_0 is the stress at which 37% of the samples survived. Using this relationship the failure distribution for the data given in Table 17 can be calculated, as shown in Figure 5-9.



Figure 5-9: Failure distributions from test data [12]

5.2.2 Ceramic capacitor Weibull modulus failure model

The distribution for the fracture strength of the ceramic can be adjusted to account for the volume of the sample, as shown in Equation 5-2.

$$\phi = \exp\left\{-\frac{V}{V_o}\left(\frac{\sigma}{\sigma_o}\right)^m\right\}$$

Equation 5-2: Failure distribution accounting for sample volume [53]

Where V_0 is the volume, or geometric parameter of the initial test specimen that describes the region where the crack may initiate. V is the geometric parameter of the sample for which the failure is to be calculated. Using the analytical stress model, the Weibull modulus, and characteristic strength can be determined from manufacturer test data. The failure initiation site will be assumed to be the area along the end termination. This means that the geometric parameter will be the width of the device. The manufacturer results are typically from three point bend tests and the given deflections must be converted to inputs suitable for the analytical model.

5.2.3 Failure Distributions

The failure of chip components under flexural loading is observed to be typically nondeterministic. The brittle nature of monolithic¹⁰ ceramics and their sensitivity to flaw

¹⁰ While ceramic capacitors are a composite structure, the additional elements provide no reinforcement against flexure events and for all practical purposes can be ignored

population triggers this probabilistic behavior. The analytical model therefore requires the selection of a distribution to describe this load-reliability relationship.

As mentioned in the previous chapters, the distribution selected was a Weibull distribution. While this distribution displayed an excellent fit to experimental measurements, the selection was based on the rationale that Weibull distribution is an extreme or lowest value distribution derived from weakest link theory [55]. This statistical approach (lends itself/maps) well to the physical mechanics that initiate chip component failure. As the application of the flexural load results in an overstress event, where initiation, rather than growth-dependent mechanisms, is the dominant factor, fracture results when the stress intensity factor evolving at the largest appropriate¹¹ flaw, i.e., the weakest link, exceeds the material fracture toughness.

A differentiation in Weibull distributions is provided by the use of two parameters or three parameters to describe the failure statistics. The criticality of this selection is inherent at the outer bounds of the distribution. This can be clearly be demonstrated in the tail ends of the distribution shown in Figure 5-10.

¹¹ Appropriate is defined as a flaw located in the volume subjected to Mode 1 tensile stress and oriented perpendicular to the applied load



Figure 5-10: Two parameter Weibull distribution fit to data

Numerous factors led to the selection of two-parameter Weibull as the appropriate distribution for predicting failure of chip components under flexural loads. While this deviates from the accepted method of fitting to three-parameter Weibull when describe the outlying behavior of solder joints subjected to thermo-mechanical fatigue [58,62] there are definitive rationales for the selection of two-parameter Weibull.

The primary driver is that three-parameter Weibull assumes a threshold stress or a failure free operating period (FFOP). This is appropriate for solder joint fatigue, as wear out requires the sequential evolution of deformation, microstructural coarsening, void formation and coalescence, and finally crack propagation [69]. Through this timedependent failure threshold, solder joints of acceptable quality are expected to remain failure-free for some minimum amount of time and the Weibull distribution becomes more dependent upon solder geometry and variations in operating environments. In fracture of monolithic ceramics subjected to uniaxial loading, there is limited evidence of a threshold stress. Numerous papers display two-parameter Weibull distribution when describing the fracture statistics of monolithic ceramics [63-68]. This approach is based upon the reality that the presence of large flaws, while of successively lower and lower probability, can never definitively be screened from the ceramic body. Transitioning from two-parameter to three-parameter Weibull distribution in describing the mechanical properties of brittle materials requires either a limitation in the criticality of the flaws present in the bulk material or an insensitivity to the flaw population in general. Examples of both can be found in the proof-testing of optical fibers [71] and the use of specialized processing techniques in the fabrication of high fracture toughness silicon nitride [70].

Neither case applies to the fracture of chip components under flexural loads. The use of powder processing to fabricate the bulk material (barium titanate, alumina) and the application of a metal termination provide avenues for the introduction of defects of significant size. Recent examinations of commercially available alumina identified pores exceeding 50 microns in diameter, even when investigating relatively small volumes [63].

An additional concern in the test data used to map the distribution behavior is the use of capacitance monitoring to identify fracture. While not definitively proven, personnel

observations (Figure 5-11) seem to suggest that capacitors that experience fracture at relatively low flexural loads display an acute angle of crack propagation.



Figure 5-11: Capacitor fracture, no capacitance drop

This can result in no loss of capacitance, as no electrodes are intersected by the fracture path. This would have the effect of obscuring the outer bound of the failure data, artificially creating three-parameter Weibull behavior.

The final justification for assuming two-parameter behavior is the unknown sample sizes available to fit these distributions. This provides insufficient data to provide any prediction of outer bound behavior, where two-parameter and three-parameter predictions begin to differentiate. Because of the need for a conservative prediction methodology, as under prediction has a severely limited value, three parameter should only be used when it demonstrates a significantly better fit to justify the need of an additional parameter, i.e. the threshold stress.

5.2.3.1 Deflection moment relationships

The input moment for the analytical stress model is calculated using the deflection relationships for three point bend tests. Initially beam equations were used and then verified with experimental results. If necessary, plate equations would be utilized. During a three point bend test the maximum moment is developed at the center of the beam. The deflection for a three point bend test using simple beam equations is shown in Equation 5-3.

$$\delta = \frac{PL^3}{48EI}$$

Equation 5-3

Where δ is the displacement at the center of the beam, P is the force applied, E is the elastic modulus, I is the second moment of inertia, and L is the length of the beam. Given a displacement the force P can be determined. The moment in the beam can than be calculated using Equation 5-4.

$$M(x) = \frac{P}{2}(x) - P\left(x - \frac{L}{2}\right)$$

Equation 5-4

Where M is the moment, L is the length of the beam, and P is the applied force. Substituting Equation 5-3 into Equation 5-4 yields the following moment, and displacement relationship, shown in Equation 5-5.

$$M(x) = \frac{24\delta EI}{L^3} \left(x \right) - \frac{48\delta EI}{L^3} \left(x - \frac{L}{2} \right)$$

Equation 5-5

If necessary this moment can then be converted to the strain in the outer fiber of the printed wiring board by using the relationship shown in Equation 5-6

$$\varepsilon = \frac{My}{EI}$$

Equation 5-6

Where y is half the thickness of the printed wiring board, M is the moment, E is the Young's modulus, and I is the moment of inertia. The resulting strain is therefore directly proportional to the moment at that location in the board.

5.2.3.2 Validation of deflection moment relationships

The validity of beam type equations is verified by conducting a three point bend test on a printed wiring board assembly. Two strain gages were mounted to an actual printed wiring board, as shown in Figure 5-12, which was then tested in a three point bend test,

as shown in Figure 5-13. The center ram was pushed up into the board and strain readings were taken at 1 mm displacement intervals. Theoretical strain calculations were made for the strain gage locations using Equation 5-5 and Equation 5-6. The results of the calculations and experiment are shown in Figure 5-14.



Figure 5-12: Test board section



Figure 5-13: Board bending test setup



Figure 5-14: Board bending experimental and theoretical results

The theoretical calculations using beam equations showed very good correlation to the actual measured strain values.

5.2.4 TDK failure parameters

The TDK Corporation has published failure data in their application manual for ceramic capacitors. The failure data from the TDK application manual for a 0805 capacitor is shown in Figure 5-15.





Figure 5-15: TDK capacitor failure data 0805 size capacitor [25]

Converting the displacement data using the analytical model to the equivalent capacitor stress yields the survival probability as a function of stress. This then allows the computation of the parameters (Table 19) necessary to use the Weibull modulus as a failure model. The failure data from the 1.6 mm board thickness was used to determine the Weibull modulus and characteristic strength values. The failure distributions are shown in Figure 5-16. Included in the graph are the failure predictions based upon parameters found in literature [12]. As shown, the literature failure parameters underpredict the probability of failure of the device. However, this is expected as these values were determined by three point bend testing on relatively short samples, which means that they may be failing in combined shear and bending.

The Weibull failure model provides a relatively good correlation with the failure data between failure probabilities of 30 to 99%. However, the error rapidly increases below 30%. The problem is that the test data does not include non-visible cracks in the capacitor that fail to intersect the electrodes. The standard capacitor flex test utilizes a drop in capacitance as its failure definition. Using this criterion excludes all cracks that are not visible or do not cause the required change in capacitance.

		Characteristic Strength	Weibull
Dielectric Type	Capacitor width	67% Failure (MPa)	modulus
TDK 0805, X7R	1.27	134.2	5.5
X7R Dielectric [12]	4.83	166	6.5

Table 19: Computed Weibull modulus from experimental data



Figure 5-16: TDK failure probability, 0805 capacitor. 1.6 mm PWB

The TDK data also includes results from tests run on a 0.8 mm thick printed wiring board. Using the failure model with the calculated parameters, and the analytical stress model, the results as a function of board displacement are shown in Figure 5-17.



Figure 5-17: TDK failure probability, 0805 capacitor, two PWB thicknesses

The results show that the analytical model combined with a manufacturer specific failure results adequately predicts failures of capacitors during printed wiring board bending. A comparison of four TDK capacitor sizes and their predicted failure distributions is shown in Figure 5-18



Figure 5-18: Capacitor size comparison

5.2.5 MuRata failure parameters

MuRata has published failure data in its application manual for MLCC capacitors [20]. MuRata did included data for three dielectric types. The failure parameters computed from this data are shown in Table 20. The experimental and analytical model results are shown in Figure 5-19.

Dielectric Type	Capacitor width	Characteristic Strength 67% Failure (MPa)	Weibull modulus
muRata 0805, Y5V	1.27	100.3	4.47
muRata 0805, X7R	1.27	100.6	5.2
muRata 0805, C0G	1.27	106	13

Table 20: Computed Weibull modulus from experimental data

The results clearly show the strengths of the various dielectrics and confirm that COG is the strongest, followed by X7R and then Y5V.



Figure 5-19: MuRata capacitor comparison, 0805

5.2.6 Syfer failure parameters

The data from Syfer is shown in Table 21. The failures are presented as interval data since they were collected at 0.5 mm displacement steps, as shown in Table 21.

Bend distance to	No. of Cracked
Crack Capacitor	Capacitors
2.5mm	31
3.0mm	79
4.0mm	158
5.0mm	171

Table 21:	Failure	data	from	Syfer	[44]
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This data was fitted to a Weibull distribution and plotted versus stress is shown in Figure 5-20.



Figure 5-20: Syfer failure data X7R 1206 capacitor

The computed Weibull modulus for the Syfer X7R 1206 capacitor is shown in Table 22.

Table 22: Comp	uted Weibull m	odulus from e	experimental data
----------------	----------------	---------------	-------------------

Dielectric Type	Capacitor width	Characteristic Strength 67% Failure (MPa)	Weibull modulus
Syfer 1206, X7R	1.524	117.5	5.12


Figure 5-21: Failure model and experimental data

5.2.7 <u>Cal-Chip failure parameters</u>

Four point bend tests were conducted on Cal-Chip Y5V capacitors. Theses capacitors had manufacturing defects present. The defect is known as micro-cracking, and it occurs near the end of the capacitor between the electrodes, as shown in Figure 5-22.



Figure 5-22: Micro-cracking in Cal-Chip Y5V capacitor (optical and ESEM images)

It was believed that the presence of these cracks could degrade the strength of the capacitors. Standard Cal-Chip capacitors are rated to a 2 mm deflection specification.

The failures were recorded at 500 $\mu\epsilon$ intervals. A Weibull plot verses stress is shown in Figure 5-20.



Figure 5-23: Cal-Chip failure data Y5V 1206 capacitor

The computed Weibull modulus for the defective Cal-Chip Y5V 1206 capacitors is shown in Table 22. These values are much lower and not reflective of a 2 mm deflection specified capacitor such as those from TDK. A plot of the failure model with the experimental results is shown in Figure 5-24.

Dielectric Type	Capacitor width	Characteristic Strength 67% Failure (MPa)	Weibull modulus
Cal-Chip 1206, Y5V	1.524	75.2	3.9

Table 23: Computed Weibull modulus from experimental data



Figure 5-24: Cal-Chip Y5V failure model and experimental results

5.2.8 Capacitor failure model summary

Experimental results from four major capacitor manufacturers have been used to develop manufacturer specific capacitor failure parameters and to demonstrate the technique for using the analytical stress model with a Weibull failure model. The steps for developing the failure parameters involved:

- Converting printed wiring board deflections into equivalent pwb moments using basic beam equations
- Converting these moments into capacitor stresses using the developed analytical model
- 3. Plotting the probability of capacitor failure as a function tensile stress

4. Fitting a Weibull distribution to the data and obtaining the Weibull modulus and characteristic strength at 67% failure, the capacitor width at which the values are taken must be retained in the failure model. This width is divided into the width of the capacitor for which failure is to be predicted.

A comparison of the failure behavior between five manufacturers for a 1206 size capacitor on a 1.6 mm thick FR-4 printed wiring board is shown in Figure 5-25. Capacitors from TDK, Cal-Chip and Syfer are rated to 2 mm maximum deflection while the MuRata capacitors are only rated to a 1 mm maximum deflection limit (see Table 3). The capacitors from Cal-Chip had defects present that may have compromised the strength of the capacitors. The results indicate that the capacitors from TDK are much stronger than the other X7R capacitors and that the presence of micro-cracking may have reduced the durability of the Cal-Chip capacitors.



Figure 5-25: Manufacturer comparison, 1206 size capacitor

5.3 Failure model, ceramic chip resistors

Flexural failure of ceramic chip resistors is far less common than ceramic capacitor failures because of the high strength of the alumina used in chip resistor construction. As stated previously there are two failure modes, resistor body cracking and end metallization separation. Experimental results indicate that these two failure modes can occur at the same stress levels [41]. These failure modes both have the same initiation sites with the difference being only in the direction of crack propagation. Therefore, this behavior suggests that only one failure model is necessary to cover both these modes. Thus, failure is defined as crack initiation and the subsequent direction of the crack is irrelevant. Experimental results for resistor failures are shown in Table 24. The stress values in column three are computed using the analytical model. These values agree with published values for bulk alumina, which are typically around 380 MPa [48]. The characteristic strength and Weibull modulus from published data is shown in Table 25.

Test	Number of Number of	Board Strain (uc)	Tensile Stress
Set	Failures		(MPa)
А	3	10,000 - 14,000	356 - 500
В	1	10,000 - 14,000	356 - 500
С	1	7,000 - 10,000	249 - 356
D	4	10,000 - 14,000	356 - 500
Ē	2	10,000 - 14,000	356 - 500
F	2	10,000 - 14,000	356 - 500

Table 24: Failure Data, 1206 Size Resistor [35]

Using the provided Weibull modulus as the failure model the predictions for the failure of the chip resistor as a function of board level strain is shown in Figure 5-26.

 Table 25: Weibull modulus from published data [48]

	Characteristic Strength	Weibull
Material	67% Failure (MPa)	modulus
Alumina	395	11



Figure 5-26: Surface mount resistor failures. 1206 size

The model predicts failure of the resistors in the measured intervals for the test data.

5.4 Summary

The analytical model has been shown to provide stress values that can be used in a stress Weibull based failure model. This failure model can than be used to predict the failures various sized capacitors and resistors. Manufacturer dependent failure parameters have been developed for the analytical stress model but should be adequate for use in finite element analyses. The techniques used can be extended to other surface mount chip devices such as ferrite beads and varistors.

CHAPTER 6 SOFTWARE IMPLEMENTATION

In this section, the analytical stress model and the failure models are implemented into a online web based calculator. The goal is to provide an engineer with a tool to rapidly assess the probability of failure for leadless chip capacitors and resistors. This will be accomplished by developing a straight forward, flexible, and intuitive interface that links to a software engine that handles the calculations. The calculator will consist of two parts.

1. HyperText Markup Language (HTML) and Javascript interface webpage

2. Java based analytical stress and failure model applet

6.1 Javascript, HTML interface

The use of HTML and Javascript to construct the user interface allows for rapid development and platform portability. The inputs and results are displayed as text which makes printing the interface with the results very easy. The interface, which is shown in Figure 6-1 uses a variety of methods for inputting the necessary parameters for the analytical model.

Pull down menus are used to enter selections for which the parameters reside within the java calculator. These parameters are predefined as to speed up the data entry process and to control the inputs to ranges or values for which the model has been verified.

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File Edit	View Favorites Tools H	elp 🌐			
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	Capacitor Cracking Calculator Probability of MLCC Cracking Due To Printed Wiring Board Bending Version 2.0				
This program typical value correspondir capacitor is a	n calculates the probability of cra es for each entry, clicking on th ng results. This allows the user to assumed to be placed on the PWB	cking an MLCC during PWB bending. Initially the form contains he Compute button at the bottom of the form will display the become familiar with the routine and see some typical results. The at the point of greatest deflection.			
	Reset The Form:	Reset			
	MLCC Manufacturer:	Generic, 2 - mm 💌			
	Dielectric Type:	X7R 💌			
	MLCC Size:	1206 Thickness: 1.0 [mm]			
	Solder Fillet Shape:	nominal			
	Solder Material:	PbSn 💌			
	Solder Pad Width:	100 [% of chip width (85-125)]			
	Solder Pad Length:	1.0 [mm]			
	Solder Thickness:	0.0635 [mm], Typically between 0.0254 and 0.127			
	PWB Thickness:	1.6 [mm]			
	PWB Modulus:	[17000 [MPa]			
	Applied PWB :	0.002 strain [%]			
	Compute Results:	Compute			
	Capacitor Stress:	[MPa]			
	Probability of Capacitor Failure: %				
Applet strate	Copyright © 2004 by <u>Nathan Blattan</u> , All Rights Reserved				
Per Applet starte	u,				

Figure 6-1: Analytical model interface

Selections that are predefined are:

- 1. MLCC manufacturer
- 2. Dielectric type
- 3. MLCC size
- 4. Solder fillet shape
- 5. Solder material
- 6. Applied PWB load type

The values for these selections reside within the java applet that implements the analytical calculations. The source code for the HTML interface can be found in Appendix 10.3.1. Once the variables are entered and selected a button is pressed that sends the values as strings to the java applet.

6.2 Java Applet, analytical model

The JavaScript interface passes the variables as strings to the Java applet. In the case of inputted numbers, the strings are converted to actual floating point numbers and assigned to the corresponding variable. The results of the menu selections are also passed as strings. These strings are compared to strings in the applet that have predefined values associated with them.

6.2.1 Internally defined variables

The first set of internally defined variables is associated with the capacitor manufacturer. The manufacturer has associated with it the variables that define the failure behavior of the capacitor. Currently there are five different choices for the capacitor manufacturer as shown in Figure 6-2.



Figure 6-2: Manufacturer selection

Associated with these selections are the values of the Weibull modulus and characteristic strength of the capacitors that define the failure behavior, as detailed in chapter 5.

The next pull down menu selects the dielectric type, as shown in Figure 6-3.



Figure 6-3: Dielectric type selection

The size selection for the capacitor involves two inputs. The pull down menu selects the industry standard size designation and the second is a numerical input for the thickness.



Figure 6-4: Capacitor size and thickness entry

The fillet shape selection has three choices, as shown in Figure 6-5.



Figure 6-5: Fillet shape selection

These descriptors refer to the joint factor coefficient specified in section 3.2.2.1.

The solder material selection is fixed to PbSn until experimental data becomes available to validate the model for different solder, such as lead-free.

6.2.2 Externally defined variables

These variables are inputted into the fields of the interface. They are then passed as strings to the applet, converted and assigned to the appropriate variable. The following variables are passed to the applet.

- 1. Capacitor thickness
- 2. Solder pad width expressed as a percentage of capacitor width
- 3. Solder pad length
- 4. Solder thickness
- 5. Printed wiring board thickness
- 6. Printed wiring board modulus
- 7. Applied PWB strain, curvature or deflection

The applied PWB input has a pull down menu associated with it, shown in Figure 6-6. This menu identifies the type of the input. These are percent strain, curvature or deflection. The deflection entry is based upon a simply supported beam with a length of 90 mm.

Applied PWB :	0.002	strain	•	[mm/mm, 1/mm, mm]
Compute Results:	Compu	strain curvature		
Capacitor Stress:		deflection [IVIPa]		

Figure 6-6: PWB load type selection

All the inputs or selections are passed as strings. An error message is displayed if no value is passed or if the values are outside the acceptable ranges.

6.2.3 <u>Computations</u>

After all the variables are assigned the applet implements the necessary equations to compute the capacitor stress and probability of failure, as detailed in chapters 2 though 4. The java code for the model can be found in Appendix 10.3.2.

CHAPTER 7 CASE STUDIES

To illustrate the use of the analytical model three case studies were conducted on industry sponsored failure analyses. Both case studies involve the failure of ceramic capacitors due to board bending. The first case study deals with failures due to printed wiring board assembly and the second involves the failures of capacitors that were later discovered to be defective.

7.1 Ceramic chip capacitor cracking, medical product

The developed failure models for ceramic chip capacitors were applied to verify the failure of a medical product during testing. The manufacturer of the device began to experience an unacceptable reject rate of the product after a temperature/humidity screen of 40°C/90%RH for eight hours. When the failure rate increased, the company performed a failure analysis to determine root-cause. The failure mode of the rejects was described as high off-state current leakage. Electrical analysis traced the failure site to two multilayer ceramic capacitors (MLCCs), C2 and C3.

Investigation by the capacitor supplier Vishay Vitramon seemed to indicate that the failure mechanism of the ceramic capacitors was cracking due to excessive flexure of the board during the manufacturing process. The company than requested an independent analysis to review these findings.

7.1.1 Initial inspection

A systematic approach to the root-cause analysis was taken, proceeding from the leastdestructive to the most-destructive until root-cause is conclusively identified. The first step in this process is visual inspection. Two samples were subjected to visual inspection with the unassisted eye. A more detailed inspection, performed at 20x using a Nikon stereoscope, was conducted to identify any gross defects. The results of visual inspection are displayed in Figure 7-1, Figure 7-2, Figure 7-3, and Figure 7-4.



Figure 7-1: (16.5x) Top view of capacitors C2 and C3



Figure 7-2: Low angle image of capacitors C2 and C3



Figure 7-3: Optical micrograph of C2, arrows mark the potential cracks



Figure 7-4: Optical micrograph of capacitor C3

The capacitors C2 and C3 on two sample boards were then electrically isolated by severing traces leading to the capacitors. Capacitance and leakage current measurements were then performed using a Sencore Model LC53 Capacitance Meter. The results from electrical measurements are displayed in Table 26.

Sample	Capacitor	Capacitance (µfarads)	Leakage Current (µamps)
	C2	0.475	0.00
Board 1			
	C3	0.477	0.00
	C2	0.492	0.00
Board 2			
	C3	0.479	0.00

Table 26: Electrical measurements of C2 and C3

While the visual inspection indicated that cracks might exist in at least one of the capacitors, the electrical measurements were inconclusive, with all measured capacitors showing nominal capacitance and no leakage current.

7.1.2 Cross sectioning

Capacitor C1 and C2 on the devices were subjected to cross-sectioning. The capacitors were first mounted in a room-temperature cure epoxy. The additional rigidity prevents relative motion during material removal. The capacitors were ground to approximately one fourth the device width using 600 and 1200 grit silicon carbide paper. The results are displayed in Figure 7-5 and Figure 7-6.



Figure 7-5: Optical micrographs of cross-sectioned capacitor C1





Figure 7-6: Optical micrographs of cross-sectioned capacitor C2

The capacitors, while testing good showed evidence of cracks. The cracks were determined to be caused by excessive board flexure. This determination is based upon the morphology of the crack, which initiates at the metal termination and propagates at a 45 degree angle through the capacitor.

7.1.3 Root cause determination

To initiate effective corrective and preventative actions, it was necessary to identify the root-cause of the flex cracking. Since the products had not been shipped to the customer, reviews of the various stages of the assembly process were characterized to identify possible flex events. The manufacturer applied strain gauges to their assembly in the location of the faulty capacitors and the board was run through the manufacturing processes. A summary of the results of this set of measurements are displayed in Table 27.

Assembly Condition	Maximum strain (με) measured
In Circuit Test – series 1	947
In Circuit Test – series 2	977
In Circuit Test – series 3	1029
Depaneling	981
LCD Insertion	389

Table 27: Manufacturing Strain Measurements

7.1.4 Analytical model, failure probability

The capacitors used were from Vishay and other manufacturers. The capacitors from Vishay were general purpose, X7R dielectric, and size 1206. These capacitors have a deflection rating of 1 mm. Since manufacturer failure data was unavailable the failure model for MuRata capacitors was used, as a conservative assumption, since MuRata

capacitors also feature a 1 mm deflection specification. The inputs to the analytical model are shown in Table 28.

Parameter	Value
Capacitor Length	3.048 mm
Capacitor Width	1.524 mm
Capacitor Thickness	1.27 mm
PWB Thickness	0.8 mm
Solder Joint Thickness	0.03 mm
Solder Pad length	1.5 mm
Solder Fillet	0.7

Table 28: Inputs to analytical model

The failure probability as a function of board level strain is shown in Figure 7-7. As shown in the graph, the 1 mm deflection capacitors have a 1% chance of failing at a board level strain of 1029 $\mu\epsilon$. The 2 mm deflection capacitors have a failure probability of less than 0.1% at the same strain level.



Figure 7-7: Failure probability as a function of board strain

7.1.5 Corrective actions

A 1% probability of failure is unacceptable on a high volume product. As an example, the customer set the maximum fallout during screen, where the failures were detected, as 160 ppm (0.016%). Based upon the strain measurements and model predictions corrective actions were suggested to reach this level.

The first corrective action was to use capacitors that have a 2 mm deflection specification, such as those from TDK. Changing capacitors alone would reduce the failure probability by a factor of 10, to about 0.1 %. Additionally, it was recommended that the manufacturer find ways to limit board bending during assembly. The two critical assembly steps were the in-circuit testing and the depaneling operation. If 1 mm capacitors are used these strain levels must not exceed 450 μ E to obtain a failure probability of 0.016%. The use of 2 mm capacitors increases the allowed board strain levels to around 700 μ E.

7.2 Ceramic chip capacitor cracking, military product

The manufacturer of a military product was experiencing an unacceptably high level of field returns. Root cause analysis identified capacitor cracking as the reason (see Figure 7-8).

The purpose of this exercise was to quantify the board-level strain that arose during depanelization and standoff attachment to confirm the root-cause of the failures. To initiate this investigation, the company provided printed wiring board panels. Each panel consisted of four boards each.



Figure 7-8: Flex cracking in a capacitor

7.2.1 Experimental testing

The first step of the study was to investigate and identify the board-level strains present in the board during depaneling and chassis mounting. The measurement of board-level strain was performed by removing the capacitors of concern and applying a strain gauge to the board in the area of interest. The black dots in Figure 7-9 indicate the locations where the strain gauges were mounted. The data acquisition system diagrammed in Figure 7-10 was used to record the strain values.

After instrumentation, the panel was subjected to a manual depaneling process. An example is shown in Figure 7-11.



Figure 7-9: Test panel with strain gauge locations marked as black dots



Figure 7-10: Data acquisition system

The strain values recorded during the depaneling operation are displayed in Figure 7-12.



Figure 7-11: Hand depaneling operation

The maximum strain value recorded during the depaneling operation was approxiametly $980 \ \mu\epsilon$.

Next the board was subjected to chassis mounting with a shim added to one of the standoffs to simulate misalignment, as shown in Figure 7-13.



Figure 7-12: Strain measurements during depaneling

Three washers were used to achieve 1.5 mm of misalignment, based on tolerances on one standoff. The mounting screws of the board were then tightened to the manufacturers specified torque values. The recorded strain values are shown in Figure 7-14. The maximum strain value recorded during the chassis mounting operation was approximately $350 \ \mu\epsilon$.



Figure 7-13: Chassis mounting with simulated misalignment



Figure 7-14: Strain measurements during mounting

7.2.2 <u>Analytical model, failure probability</u>

The next step was to calculate the probability of failure for the maximum strains seen during the testing, which were approximately 940 $\mu\epsilon$. The analytical model was used with the input shown in Table 29.

Parameter	Value
Capacitor Length	3.048 mm
Capacitor Width	1.524 mm
Capacitor Thickness	1.00 mm
Capacitor End Margin	0.5 mm
PWB Thickness	1.6 mm
Solder Joint Thickness	0.035 mm
Solder Pad length	1.3 mm
Solder Fillet, Nominal	0.7

 Table 29: Inputs to analytical model

The failure model used was that for capacitors from Syfer, MuRata and TDK which are 1 and 2 mm spec capacitors, since no test data was available for the Cal-Chip capacitors used on the boards.

The results from the analytical and failure model are shown in Figure 7-17. According to these results the 2 mm spec capacitors should have between 0.01% and a 0.05% probability of failure and the 1 mm spec capacitors should have a failure probability

around 0.08%. This is much less than the observed field return percentages. Further investigation into the failure behavior of the Cal-Chip capacitors was needed.

7.2.3 <u>Cal-Chip capacitor microscopy</u>

To investigate the quality of the capacitors additional optical and electron microscopy was preformed. Optical inspection revealed a manufacturing defect known as microcracking. Micro-cracks are typically a result of excess electrode material being deposited in the end margin. This excess metallization causes excessive residual stresses to develop in the ceramic near the end-cap which leads to the micro-cracking. The details of the micro-cracks observed are shown in Figure 7-15. Further experiments were conducted to assess the strength of these defective capacitors and to develop an appropriate failure model.



Figure 7-15: Micro-cracking in Cal-Chip Y5V capacitor (optical and ESEM images)

7.2.4 <u>Cal-Chip capacitor bend testing</u>

The test coupon utilized is a custom design that was specifically developed for conducting four point bend tests on 1206 and 0603 sized components. It is a four layer FR4 board and is 0.062 inches thick and is shown in Figure 7-16. Eight capacitors and two strain gauges were mounted on the test coupon.

The board was placed into the MTS machine and subjected to deflections that produced board surface strain values in 500 $\mu\epsilon$ increments. The results of the testing are shown in Table 30.



Figure 7-16: Bend test coupon

These results were used to develop the Cal-Chip capacitor failure model in section 5.2.7.

Identifier	Capacita	Failure Strain	
	Before Bend Testing	After Bend Testing	(με)
C1	1.07	0.21	2000 - 2500
C2	1.07	0.12	2000 - 2500
C3	1.07	0.12	2500 - 3000
C4	1.07	1.07	> 3000
C5	1.07	0.60	1500 - 2000
C6, C7, C8	1.07	1.08	> 3000

Table 30: Bend testing results, Cal-Chip Capacitor

7.2.5 Cal-Chip capacitor analytical results

Using the new failure model, the analytical model was exercised again to compare the Cal-Chip capacitors to other capacitors. The results are shown in Figure 7-17.



Figure 7-17: Probability of failure, board depaneling with Cal-Chip capacitor

The results show that at the observed strain levels the Cal-Chip capacitor has a probability of failure 17 times higher than capacitors from MuRata, 27 times higher than capacitors from Syfer, and 135 times higher than capacitors from TDK. Since the Cal-Chip capacitors are rated similarly to those from TDK and Syfer one would expect a similar failure behavior.

7.2.6 Corrective actions

The failure probability of the defective capacitors was shown to be too high by the number of field returns and the analytical model. The main recommendation was to stop using the defective capacitors from Cal-Chip and to rework the boards to replace the
defective capacitors. As predicted by the model, normal capacitors of both 1 and 2 mm deflection should have very low failure probabilities under the applied printed wiring board bending. Additional robustness can be gained by using 2 mm specified capacitors from a well known manufacturer like TDK.

7.3 Ceramic chip capacitor cracking, defense product

The developed failure models for ceramic chip capacitors were applied to verify the failure of a defense product. This is a high reliability product and the manufacturer was experiencing a 5% failure rate during product qualification because of capacitor cracking.

Root cause investigation identified capacitor C73, as shown in Figure 7-18, as the cause of the failure. Based upon the capacitors location, the cause of the failure was suspected to be cracking due the development of strain during tightening of standoffs to the board or standoffs to the housing mechanism.



Figure 7-18: Failed capacitor C73, next to board standoff

7.3.1 Cross-sectioning

Capacitor C73 was removed and cross-sectioned to identify the failure. As shown in Figure 7-19, the capacitor had a crack present that was consistent with those associated with flexural failures.



Figure 7-19: (32x) Optical micrograph of C73

7.3.2 Experimental testing

Two capacitors were removed from the board at locations close to the standoffs. Strain gages were mounted in these locations, as shown in Figure 7-20, so that the strain values during board mounting and connector attachment could be monitored and recorded. The data was collected in two steps. Step one involved the mounting of the board to the chassis, as shown in Figure 7-21 and step two involved attaching the connectors to the chassis, as shown in Figure 7-22. The strain values were recorded as the mounting screws were tightened to specified torque amounts.



Figure 7-20: Strain gage mounting locations, C73 and C63



Figure 7-21: Board to chassis mounting



Figure 7-22: Connector to chassis mounting

The strains recorded at various torque levels are shown in Table 31 and Table 32.

· · · · · · · · · · · · · · · · · · ·	Board Surface S		
Torque (cN-m)	Standoff to Board	Comments	
20	-23	291	
40	-76	699	
60	-93	699	
80	-93	723	
100	-105	1026	Stripped one standoff

Table 31: Surface strain	measured at location	of capacitor	C73
	measurea at recurrent	or capacitor	~ . •

Table 32: Surface strain measured at location of capacitor C63

	Board Surface S		
Torque (cN-m)	Standoff to Board	Comments	
20	52	449	
40	76	425	
60	76	583	
80	117	723	
100	146	874	Stripped one standoff

As shown in the tables the higher strain corresponded to higher torque settings. The manufacturer had specified a torque setting of 80 cN·m and strain values of 723 were recorded at both locations at this setting.

7.3.3 Capacitor analytical results

The values used in the analytical capacitor failure model are shown in Table 33. These values were determined by measurements taken from the actual device. The capacitors were reported to be manufactured by AVX with a 2 mm deflection specification. Since failure data for AVX capacitors was unavailable the failure parameters developed for Syfer capacitors was used.

Parameter	Value
Capacitor Length	3.048 mm
Capacitor Width	1.524 mm
Capacitor Thickness	1 mm
Capacitor End Margin	0.5 mm
PWB Thickness	1.6 mm
Solder Joint Thickness	0.035 mm
Solder Pad length	1.7 mm
Solder Fillet, Nominal	0.7

 Table 33: Inputs to analytical model

As shown in Figure 7-23, at these strain levels the capacitor should have a failure probability of less than 0.06 %.



Figure 7-23: Probability of capacitor failure as a function of PWB strain

7.3.4 Discussion

The analytical model did not predict flexural failures based upon the results of the tests. In a previous case study the discrepancy was experienced because of defective capacitors. In this case the capacitors did not appear to be defective. There are three other potential reasons for the discrepancy. One, the capacitors could be counterfeit and less robust to flex events then the capacitors from the intended supplier or the strain values measured may be lower than those actually present. There is also the possibility that the manufacturer was just extremely unlucky, based on the limited sample set (20 assemblies) this may be a possibility. The recommendations to the manufacturer were to verify the authenticity of the capacitors, limit the torque settings to $60 \text{ cN} \cdot \text{m}$, and to consider applying strain relief between standoffs.

7.4 Summary

The analytical model has been employed in a series of case studies to illustrate its application and usefulness. The results of these studies confirmed the root cause of the failures and provided the companies the information required to facilitate corrective actions.

CHAPTER 8 CONCLUDING REMARKS

The value of this research effort has been in identifying the physical mechanism that initiates failure in ceramic bodies attached to a glass fiber/epoxy matrix composite in a non-compliant manner, assessing the response of this mechanism to various geometries and mechanical loading conditions, and developing an analytical model that allows the user to assess risk during the design phase and to determine the root cause of field failures.

Previous attempts at resolution have failed to address the root-cause (Mode I stress condition in the ceramic capacitor). As a result, they are of limited value, especially to the end user, and prevent the designer the ability for a more nuanced assessment of risk (prior work focused on go/no-go)

Development of a closed form analytical model for rapidly assessing the failure of leadless ceramic chip components has been completed and applied to ceramic chip resistors and capacitors. The model utilizes classical approaches to structures and fracture to make failure predictions. The model is comprised of two sections, the stress analysis, and probability of failure analysis.

The stress analysis model has been verified and modified based upon the results of numerous 2D and 3D finite element models. Modification of the model utilizes a stress concentration factor and an additional shear spring to represent the surface behavior of

the printed wiring board. These are relatively simple equations that are easily explained. The resulting maximum stresses of the device are very close to those predicted by FEA.

These stresses are then used in Weibull based failure models to predict the probability of component failure with regards to printed wiring board bending. Failures parameters from literature for alumina have been shown to provide relatively good predictions of chip resistors failures with the stress values computed by the analytical stress model. Further accuracy can be obtained by using available manufacturers test data to develop manufacturer specific failure models.

The analytic model does deviate from the manufacturer test data with regard to low stress level failures. The reasons for this may reside in the test standards the manufacturers use for these tests. The standard specifies that a drop in capacitance or visual cracks indicate a failure. This criterion eliminates the capturing of two types of failures, non-visual cracks that do not intersect the electrodes, or non-visual cracks that do not drop the capacitance enough to be registered as a failure. The current standard therefore makes some cracking acceptable. This is not adequate because it fails to recognize that the crack may propagate under additional thermal or mechanical stresses. The analytical model assumes that any cracking is a reliability concern and should be avoided. In this regard the model actually seems to predict failures closer to those seen in the field and demonstrated by the case studies.

The analytical model can be used to generate part survivability plots that are functions of various part geometric parameters. Assuming an acceptable failure probability range between of 0.1% and 1% a plot can be generated for the use of various size components under board flexure type loads. An example graph for the acceptable surface strain values for 1 mm thick capacitors (2 mm deflection specification) of various sizes is shown in Figure 8-1.



Figure 8-1: Acceptable strain values for various size capacitors

Graphs such as these can be developed for a variety of geometric configurations and can greatly aid designers by allowing them to set strain limits for their designs.

CHAPTER 9 FUTURE WORK

The closed form analytical model developed can be extended to handle a variety of leadless chip components. The failures of devices such as varistors, and ferrite beads could be predicted after suitable failure parameters are developed and validated.

Currently, the model is only validated for standard tin-lead eutectic solder. It could be extended to calculate the failure of leadless chip components that are connected with lead-free solders. There seems to be conflicting theories on the effects that solders such as tin silver copper (SnAgCu) will have on board flexing related failures. SnAgCu is the prime candidate solder in the United States to replace PbSn for lead-free soldering. Some tests indicate that the modulus may be lower than that of eutectic tin-lead. However, solder manufacturers categorize SnAgCu as a stiff solder, relative to tin-lead. Initial calculations using the analytical stress model using SnAgCu properties determined by Weise [47] indicate that the probability of failure may increase with this solder. Mechanical testing of SnAgCu and bend testing of soldered components must be carried out before this can be validated.

CHAPTER 10 APPENDICES

10.1 Capacitor dimensions

Thickness		Chip Thickness	Qty per Reel 7"	Qty per Reel	Qty per Reel 7*	Qty per Reel	Qty per Bulk
Code	Chip Size	Range (mm)	Plastic	13" Plastic	Paper	13" Paper	Cassette
44	0201	30 + 03	N/A	N/A	15,000	N/A	N/A
PB.	0402	50 + 05	N/A	N/A	10,000	50 000	50.000
CB	0603	.80 ± .07	N/A	N/A	4,000	10,000	15,000
CC	0603	.80 ± .10	N/A	N/A	4.000	10.000	N/A
DB	0805	.60 ± .10	N/A	N/A	N/A	N/A	10,000
DC	0805	.78±.10	4,000	10,000	4,000	10,000	N/A
DO	0805	.90 ± .10	4,000	10,000	N/A	N/A	N/A
DE	0805	1.00 ± .10	2,500	10,000	N/A	N/A	N/A
DF	0805	1.10 ± .10	2,500	10,000	N/A	N/A	N/A
DG	0805	1.25 ± .15	2,500	10,000	N/A	N/A	N/A
DH	0805	1.25 ± .20	2,500	10,000	N/A	N/A	N/A
EB	1206	.78 ± .10	4,000	10,000	4,000	10,000	N/A
EC	1206	.90 ± .10	4,000	10,000	N/A	N/A	N/A
ED	1206	1.00 ± .10	2,500	10,000	N/A	N/A	N/A
EE	1206	1.10 ± .10	2,500	10,000	N/A	N/A	N/A
EF	1206	1.20 ± .15	2,500	10,000	N/A	N/A	N/A
EG	1206	1.60 ± .15	2,000	8,000	N/A	N/A	N/A
EH	1206	1.60 ± .20	2,000	8,000	N/A	N/A	N/A
EJ	1206	1.70 ± .20	2,000	8,000	N/A	N/A	N/A
FB	1210	.78 ± .10	4,000	10,000	N/A	N/A	N/A
FC	1210	.90 ± .10	4,000	10,000	N/A	N/A	N/A
FD	1210	.95±.10	4,000	10,000	NA	N/A	N/A
FE	1210	1.00 ± .10	2,500	10,000	NA	N/A	N/A
FF	1210	1.10 ± .10	2,500	10,000	NA	N/A	N/A
FG	1210	1.25 ± .15	2,500	10,000	N/A	N/A	N/A
FH	1210	1.55 ± .15	2,000	8,000	NA	N/A	N/A
FJ	1210	1.85 ± .15	2,000	8,000	NA	N/A	N/A
FK	1210	2.10 ± .20	2,000	8,000	N/A	N/A	N/A
GB	1812	1.00 ± .10	1,000	4,000	NA	N/A	N/A
GC	1812	1.10±.10	1,000	4,000	NA	N/A	N/A
GÐ	1812	1.25 ± .15	1,000	4,000	NA	N/A	N/A
GE	1812	1.30 ± .10	1,000	4,000	NA	N/A	N/A
GF	1812	1.50 ± .10	1,000	4,000	NA	N/A	N/A
GG	1812	1.55 ± .10	1,000	4,000	N/A	N/A	N/A
GH	1012	1.40 ± .15	1,000	4,000	N/A	N/A	N/A
63	1812	1./0±.15	1,000	4,000	N/A	N/A	N/A
HB	1825	1.10±.15	1,000	4,000	N/A	N/A	N/A
HD	1825	1.30 ± .15	1,000	4,000	N/A	N/A	N/A
HE	1020	1.40 ± .15	1,000	4,000	NA	N/A	N/A
HF	1825	1.50 ± .15	1,000	4,000	N/A N/A	N/A	N/A
36	2220	1.00 ± .15	1,000	4,000	N/A N/A	DVA NVA	N/A
10	2220	1.10 ± .15	1,000	4,000	N/A N/A	N/A	N/A
10	2220	1.30±.15	1,000	4,000	N/A N/A	N/A	N/A
JE	2220	1.40 ± .15	1,000	4,000	N/A N/A	NVA NVA	N/A
JF KD	2220	1.00±.15	1,000	4,000	N/A N/A	N/A N/A	N/A
KC	2220	1.10 ± .15	1,000	4,000	NA	N/A	N/A
KD KD	2220	1.10±.10	1,000	4,000	N/A N/A	NVA NVA	N/A
KE	2225	1.30 ± .15	1,000	4,000	N/A N/A	N/A	N/A
NE.	2220	1.40±.15	1,000	4,000	1104	N/A	n/A

THICKNESS CODE REFERENCE CHART PACKAGING QTY BASED ON FINISHED CHIP THICKNESS SPECIFICATIONS

This chart refers to ceramic chip thickness codes on pages 50-53.

Figure 10-1: Kemet capa	itor thickness chart	[34]
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Figure 10-2: Kemet capacitor solder pad dimensions [34]

CAP.	CAP	CAP		(00402					c	0603*							C0805	5					С	1206"			
PF	CODE	TOL.	6.3V	10V	16V	25V	50V	6.3V	10V	16V	25V	50V	100V	200V	6.3V	10V	16V	25V	50V	100V	200V	6.3V	10V	16V	25V	50V	100V	200V
150 150 220 270 330 370 470 560 560 560 1200 1000 1200 1000 1200 10000 1000 1000 1000 10000 1000 1000 1000 10	151 181 221 331 471 1551 4751 1522 2722 2722 2722 2722 2722 2722 2	KMJ KMJ KMJ				855555555555555555555555555555555555555	85 85 85 85 85 85 85 85 85 85 85 85 85 8	8 5555588888888888888888888888888888888	සි. ප්. ප්. ප්. ප්. ප්. ප්. පේ. පේ. පේ. පේ. පේ. පේ. පේ. පේ. පේ. පේ	පිස්ස්ස්ස්ස්ස්ස් පපපපපපපපපපපපපපපපපපපපපපප	සිසි සිසිසිසිසිසි සිසිසිසිසිසිසිසිසිසිස	888888888888888888888888888888888888888	888888888888888888888888888888888888888	888888888888888888888888888888888888888			CCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCCC				888888888888888888888888888888888888888				និងនិង និងនិងនិងនិងនិងនិងនិងនិងនិងនិងនិងនិងនិងន			

X7R CAPACITANCE RANGE - (0402.0603.	0805.1206
Mill Of a Horn aloc realise	1021 00001	00001 1200

NOTE: For non-standard capacitance values or voltages, contact your local KEMET sales representative. #X7R delectric - Extended Range Values - Cap and DF measured @ 0.5 Vims.

Figure 10-3: (Capacitor thic	kness codes [[34]
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CAP.	CAP	CAP.			(C1210	k.				C1812	t	C1825*			C2220			C2225		
PF	CODE	TOL.	6.3V	10V	16V	25V	50V	100V	200V	50V	100V	200V	50V	100V	200V	50V	100V	200V	50V	100V	200V
CAP. PF 2200 3300 3000 4700 6800 8200 10,000 12,000 15,000 12,000 15,000 12,000 12,000 12,000 12,000 12,000 12,000 12,000 12,000 12,000 10,000 10,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 120,000 100,000	CAP CODE 222 332 382 472 662 882 822 103 183 183 223 273 383 473 563 883 883 883 883 883 8104 124 124 124 224 274	CAP. TOL. KMJ KMJ KMJ KMJ KMJ KMJ KMJ KMJ KMJ KMJ	6.3V 日本市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市市	₽ ~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~~	16V 股股股股股股股股股股股股股股股股股股股股股股股股股股股股	C1210 25V FBBEBEBEBEBEBEBEBEBEBEBEBEBEBEBEBEBEBEB	50V 50V 50V 50V 50V 50V 50V 50V 500 500		2007 時期時期時期時期時期時期時期時期時代以及主義	50V 666666666666666666666666666666666666	C18121 100V BBBBBBBBBBBBBBBBBBBBBBBBBBBBBBBBB	200V 86568868888888888888888888888888888888	50V 900 900 900 900 900 900 900 900 900 9	1925 100V ##################################	* 2000	50V	C2220 100V	200V	50V	22255 100V 200V 200V 200V 200V 200V 200V 200V	
330,000 390,000 470,000 580,000 820,000 1,000,000 1,500,000 1,500,000 1,800,000 2,200,000	334 394 474 584 884 824 105 125 155 185 225	KMJ KMJ KMJ KMJ KMJ KMJ KMJ KMJ		유유유 유유 유유 유 유 유 유 유 유 유 유 유 유 유 유 유 유	유유유 유유 유유 유규 유규 유		FD# FD# FD# FD# FD# FD# FF# FH#	FD#		GB BBCCCE GCCE GCCE GCCE GE	ĞН		<u>₽₽₽₽₽₽₽₽₽₽₽</u>		HBHD		H H H H H H H H H H H H H H H H H H H	çç	88888888888888888888888888888888888888	000000000	

X7R CAPACITANCE RANGE - 1210, 1812, 1825, 2220, 2225

Indicates EIA preferred chip sizes.
NOTE: For non-standard capacitance values or voltages, contact your local KEMET sales representative.
 S0 Volt Ceramic Chips can be used for 63 volt applications.
 # Extended Range Values — Cap and DF measured @ 0.5 \ms.

Figure 10-4: Capacitor thickness codes (continued) [34]

CAPACITOR OUTLINE DRAWINGS



DIMENSIONS—MILLIMETERS AND (INCHES)

EIA SIZE CODE	METRIC SIZE CODE (Ref only)	L # LENGTH	W # WIDTH		B BANDWIDTH	S MIN. SEPARATION	MOUNTING TECHNIQUE
0402"	1005	1.0 (.04) ± .05(.002)	0.5 (.02) ± .05 (.002)		0.20 (0.008)-0.40 (0.016)	0.3 (.012)	Solder Reflow
0603"	1608	1.6 (.063) ± 0.15 (.006)	0.8 (.032) ± 0.15 (.006)	See pages	0.35 (.014) ±0.15 (.006)	0.7 (.028)	
0805"	2012	2.0 (.079) ± 0.2 (.008)	1.25 (.049) ± 0.2 (.008)	49 EQ for	0.5 (.02) ±.25 (.010)	0.75 (.030)	Solder Wave †
1206"	3216	3.2 (.126) ± 0.2 (.008)	1.6 (.063) ± 0.2 (.008)	40-52 IOF	0.5 (.02) ±.25 (.010)	N/A	Solder Reflow
1210*	3225	3.2 (.126) ± 0.2 (.008)	2.5 (.098) ± 0.2 (.008)	thickness	0.5 (.02) ±.25 (.010)	N/A	
1812	4532	4.5 (.177) ± 0.3 (.012)	3.2 (.126) ± 0.3 (.012)	dimensions.	0.6 (.024) ±.35 (.014)	N/A	
1825*	4564	4.5 (.177) ± 0.3 (.012)	6.4 (.252) ± 0.4 (.016)		0.6 (.024) ±.35 (.014)	N/A	Solder
2220	5650	5.6 (.220) ± 0.4 (.016)	5.0 (.197) ± 0.4 (.016)		0.6 (.024) ±.35 (.014)	N/A	Reflow
2225	5664	5.6 (.220) ± 0.4 (.016)	6.3 (.248) ± 0.4 (.016)		0.6 (.024) ±.35 (.014)	N/A	

*Note: Indicates EIA Preferred Case Sizes (Tightened tolerances apply for 0402, 0603, and 0805 packaged in bulk cassette, see page 65.) #Note: These thicknesses are EIA maximums. Most chips are considerably thinner. Consult factory for details. Also, some extended values may be slightly thicker than EIA maximums. † For extended value 1210 case size – solder reflow only.

Figure 10-5: Typical capacitor dimensions [34]

10.2 Material properties

10.2.1 Solders

Elastic Modulus for Pb37Sn63 solder:

E = 27000 MPa [47]

Elastic Modulus for AgCuSn solder:

E = 36000 to 44000 MPa [47]



Typical values compiled by Wiese of Young's Modulus from various sources.

Figure 10-6: Solder properties [47]

10.2.2 Printed wiring board

The flexural modulus for a 0.062 - 4 layer printed wiring board were determined using a 3 point bend DMA testing technique. Four boards were tested, three with metallization and one without, the results are shown in Table 34.

	Board 44	Board 17	Board 26	Board
	4245544	4245417	4245426	No copper
Freq				Baseline
rad/sec	МРа	МРа	МРа	МРа
12.53	20143	17542	19590	16369
15.77	20140	17538	19589	16383
19.86	20185	17567	19599	16400
25.00	20205	17598	19639	16419
31.47	20228	17642	19685	16436
39.62	20268	17708	19733	16474
49.88	20282	17773	19720	16490
62.80	20312	17772	19767	16525
79.06	20344	17856	19823	16563
99.53	20407	17938	19902	16622
125.30	20474	18049	19981	16696
157.75	20558	18156	20092	16772
198.59	20705	18315	20259	16904
250.01	20897	18513	20453	17071
314.75	21183	18822	20729	17335

Table 34: Flexural modulus of FR-4 at room temperature

10.2.3 Capacitors

Physical Constant	X7R	COG (NPO)	Y5V
Elastic Modulus (MPa)	110000 - 120000	120000 - 130000	90000 -
[18]			100000
Tensile Strength (MPa)	62	103	43
[18]	02	105	С т
Bending Strength (MPa)	88	137	69
[18]	00	157	07
Coefficient of Thermal	$11 - 12 \ge 10^{-6}$	$8 - 10 \times 10^{-6}$	$11 - 12 \times 10^{-6}$
Expansion 1/°C [18]	11 12 11 10	0 10 11 10	11 12 11 10
Fracture Toughness	0.6 – 1.2 [18]	1.4 [18]	
(MPa.m ^{1/2})	1.03 [12]	1.5 [12]	

Table 35: Capacitor dielectric properties

Table 36: Physical properties of metals used in capacitors [18]

Physical Constant	Ag	Cu	AgPd	Sn	Ni
Elastic Modulus (Gpa)	82 [13]	110-120	150	42	210
Yield (MPa) 0.005	50-60 [13]		80		
CTE 1/°C	20 [13]				

EIA	Class	Temperature	Barium	Other dopants	Grain size
designation		range (°C)	Titanate		(µm)
			content (%)		
NPO	1	-55 to 125	10-50	TiO ₂ ,CaTiO ₃ ,	1
(COG)				$Nd_2Ti_2O_7$	
X7R (BX)	2	-55 to 125	90-98	MgO,MnO,Nb ₂ O ₅ ,	<1.5
				CoO Rare-earth	
Z5U	2	10 to 85	80-90	CaZrO ₃ , BaZrO ₃	3-10
Y5V	2	-30 to 85	80-90	CaZrO ₃ , BaZrO ₃	3-10

 Table 37: Typical ceramic dielectric materials for MLCC [50]

10.2.4 Capacitors

MECHANICAL & ENVIRONMENTAL CHARACTERISTICS

	SPECIFICATION	TEST PARAMETERS
SOLDERABILITY:	Solder coverage 90% of metalized areas No termination degradation	Preheat chip to 120°-150°C for 60 sec., dip terminals in rosin flux then dip in Sn62 solder @ 240°±5°C for 5±1 sec
RESISTANCE TO SOLDERING HEAT:	No mechanical damage Capacitance change: ±2.5% or 0.25pF Q>500 I.R. >10 G Ohms Breakdown voltage: 2.5 x WVDC	Preheat device to 80°-100°C for 60 sec. followed by 150°-180°C for 60 sec. Dip in 260°±5°C solder for 10±1 sec. Measure after 24±2 hour cooling period
TERMINAL ADHESION:	Termination should not pull off. Ceramic should remain undamaged.	Linear pull force* exerted on axial leads soldered to each terminal. *0402 2.0lbs, 0603 2.0lbs (min.)
PCB DEFLECTION:	No mechanical damage. Capacitance change: 2% or 0.5pF Max	Glass epoxy PCB: 0.5 mm deflection
LIFE TEST:	No mechanical damage Capacitance change: ±3.0% or 0.3 pF Q>500 I.R. >1 G Ohms Breakdown voltage: 2.5 x WVDC	Applied voltage: 200% rated voltage, 50 mA max. Temperature: 125°±3°C Test time: 1000+48-0 hours
THERMAL CYCLE:	No mechanical damage. Capacitance change: ±2.5% or 0.25pF Q>2000 I.R. >10 G Ohms Breakdown voltage: 2.5 x WVDC	5 cycles of: 30±3 minutes @ -55°+0/-3°C, 2-3 min. @ 25°C, 30±3 min. @ +125°+3/-0°C, 2-3 min. @ 25°C Measure after 24±2 hour cooling period
HUMIDITY, STEADY STATE:	No mechanical damage. Capacitance change: ±5.0% or 0.50pF max. Q>300 I.R. 1 G-Ohm Breakdown voltage: 2.5 x WVDC	Relative humidity: 90-95% Temperature: 40°±2°C Test time: 500 +12/-0 Hours Measure after 24±2 hour cooling period
HUMIDITY, LOW VOLTAGE:	No mechanical damage. Capacitance change: ±5.0% or 0.50pF max. Q>300 I.R. = 1 G-Ohm min. Breakdown voltage: 2.5 x WVDC	Applied voltage: 1.5 VDC, 50 mA max. Relative humidity: 85±2% Temperature: 40°±2°C Test time: 240 +12/-0 Hours Measure after 24±2 hour cooling period
VIBRATION:	No mechanical damage. Capacitance change: ±2.5% or 0.25pF Q>1000 I.R. 10 G-Ohm Breakdown voltage: 2.5 x WVDC	Cycle performed for 2 hours in each of three perpendicular directions Frequency range 10Hz to 55 Hz to 10 Hz traversed in 1 minute. Harmonic motion amplitude: 1.5mm

Figure 10-7: Johanson Dielectrics specification page (0.5 mm) [43]

10.3 Software implementation of analytical model

10.3.1 Interface

```
The HTML and Javascript code for the model interface:
[Start here]
<html>
<head>
<title>Capacitor Cracking Calculator (v2.0)</title>
</head>
<script language=JavaScript>
// Ceramic Chip Cracking Calculator
// by: Nathan Blattau
// CALCE University of Maryland at College Park
// Do not distribute
//
function select item(name, value)
{
    this.name=name;
    this.value=value;
function get selection(select object)
ł
    contents=new select item();
    for (var i=0;i<select object.options.length;i++)
    if (select object.options[i].selected==true){
         contents.name=select object.options[i].text;
         contents.value=select object.options[i].value;
     }
    return contents;
function clearForm(form){
       form.pad width.value="100";
       form.pwb thick.value="1.6";
       form.pwb_deflect.value="2";
function computeForm(form){
       try {
              mlccMaker = get selection(form.cap man).name;
              mlccSize = get selection(form.cap type).name;
              solderJoint = get selection(form.solder type).name;
              solderPad = form.pad width.value;
              pwbThickness = form.pwb thick.value;
              pwbStrain
                              = form.pwb strain.value;
              var app = document.CapCrackCalc;
```

```
if (app == null) {
                      alert ("Java is not currently installed and/or enabled"
                             + " on this browser,\nwhich means that you can't"
                             + " use the best capacitor cracking\ncalculator"
                             + " ever made. Sorry."
                      );
                      return;
              app.computeResults (
                      mlccMaker, mlccSize,
                      solderJoint, solderPad,
                      pwbThickness,
                      pwbDeflection
                      );
              form.cap fail.value = app.getCapFailure();
              form.pwb moment.value = app.getMoment();
              form.cap stress.value = app.getStress();
       } catch (ex) {
              form.cap fail.value = "";
              msg = ex.message;
              if (msg.substring(0,21) == "java.lang.Exception: ")
                      msg = msg.substring(21);
              alert (msg);
</SCRIPT><BODY vLink=#ff00ff aLink=#ffff00 link=#0000ff bgColor=#ffffff>
<H2 style='margin:0; font-size=14pt'>Capacitor Cracking Calculator</H2>
<H3 style='margin:0; font-size=11pt'>
Probability of MLCC Cracking<br>
br>Due To Printed Wiring Board Bending
</H3>Version 2.0Control 2.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.02.0
```

```
This program calculates the probability of cracking an
```

}

}

<CENTER>

}

MLCC during PWB bending. Initially the form contains typical values for each entry, clicking on the Compute button at the bottom of the form will display the corresponding results. This allows the user to become familiar with the routine and see some typical results. The capacitor is assumed to be placed on the PWB at the point of greatest deflection. <HR noShade>

<style>TD { font-size: 10pt; } INPUT { font-size: 10pt; } SELECT { font-size: 10pt; } </style><center><FORM name=form method=post style='margin:0'> <TABLE cellSpacing=4 cellPadding=1 style='margin:0'>

<TBODY> < TR ><TD align=right bgcolor=#efefef>Reset The Form:</TD> <TD><INPUT Onclick=clearForm(this.form) type=reset value=" Reset"> </TD></TR> < TR ><TD align=right bgcolor=#bdd6ef>MLCC Manufacturer:</TD> <TD><SELECT name=cap man> <OPTION selected>Generic, 1 - mm</option> <OPTION selected>Generic, 2 - mm</option> <OPTION>Syfer</option> <OPTION>muRata</option> <OPTION>TDK</option> </SELECT></TD></TR> <TR><TD align=right bgcolor=#bdd6ef>Dielectric Type:</TD> <TD><SELECT name=diel type> <OPTION selected>Y5V</option> <OPTION selected>X7R</option> <OPTION>NP0, C0G</option> </SELECT></TD></TR> <TR> <TD align=right bgcolor=#bdd6ef>MLCC Size:</TD> <TD><SELECT name=cap type> <OPTION selected>1206</option> <OPTION>0805</option> <OPTION>0603</option> <OPTION>1210</option> <OPTION>1808</option> <OPTION>1812</option> <OPTION>1825</option> <OPTION>2220</option> <OPTION>2225</option> <OPTION>3640</option> <OPTION>0000</option> </SELECT> Thickness: <INPUT size=5 value=1.0 name=chip thick> [mm]</TD></TR> <TR><TD align=right bgcolor=#bdd6ef>Solder Fillet Shape:</TD> <TD><SELECT name=solder type> <OPTION selected>nominal</option> <OPTION>starved</option> <OPTION>bulbous</OPTION> </SELECT></TD></TR> <TR><TD align=right bgcolor=#bdd6ef>Solder Material:</TD> <TD><SELECT name=solder mat> <OPTION selected>PbSn</option> <OPTION>SnAgCu</option> </SELECT></TD></TR>

<TR><TD align=right bgcolor=#bdd6ef>Solder Pad Width:</TD>

<TD><INPUT size=5 value=100 name=pad_width>[% of chip width

(85-125)]</TD></TR>

<TR>

<TD align=right bgcolor=#bdd6ef>Solder Pad Length:</TD>

<TD><INPUT size=5 value=1.0 name=pad_length>[mm] </TD></TR>

<TR>

<TD align=right bgcolor=#bdd6ef>Solder Thickness:</TD>

<TD><INPUT size=5 value=0.0635 name=solder_thick> [mm], Typically between 0.0254 and 0.127</TD></TR>

<TR><TD align=right bgcolor=#bdd6ef>PWB Thickness:</TD>

<TD><INPUT size=5 value=1.6 name=pwb thick> [mm]</TD></TR>

<TR><TD align=right bgcolor=#bdd6ef>PWB Modulus:</TD>

<TD><INPUT size=5 value=17000 name=pwb mod> [MPa]</TD></TR>

<TR><TD align=right bgcolor=#bdd6ef>Applied PWB :</TD>

<TD><INPUT size=5 value=0.002 name=pwb_load> <SELECT name=load_type> <OPTION selected>strain [%]</option>

<OPTION>curvature [1/mm]

<OPTION>deflection [mm]</OPTION>

</SELECT></TD></TR>

<TR><TD align=right bgcolor=#efefef>Compute Results:</TD>

<TD><INPUT Onclick=computeForm(this.form) type=button

value=Compute></TD></TR>

<TR><TD align=right bgcolor=lightgreen>Capacitor Stress:</TD>

<TD><INPUT size=8 name=cap_stress style='font-weight:bold; background:

lightyellow'>[MPa] </TD></TR>

<TR>

<TD align=right bgcolor=lightgreen>Probability of Capacitor Failure:</TD> <TD><INPUT size=8 name=cap fail style='font-weight:bold;

background: lightyellow'>% </TD></TR>

<TR><TD></TD>

<TD></TD></TR></TR></TRODY></TABLE></FORM></center>

<HR noShade><center>

Copyright & copy; 2004 by

Nathan Blattau, All Rights Reserved </center><center>

<t

Java is not currently installed and/or enabled on this browser, which means that you can't use the best capacitor cracking calculator ever made. Sorry.

</applet></center></center></center>

10.3.2 Java based analytical model

```
import java.applet.*;
import java.io.*;
import java.awt.*;
import java.text.*;
import java.util.*;
public class CapCrackCalc extends Applet
ł
//
//
       Formatting the data passed from the applet to the webpage
//
       private DecimalFormat failureFmt = new DecimalFormat("000.00000");
       private DecimalFormat stressFmt = new DecimalFormat("000.00000");
//
//
       Applet output variables
//
       private double cap fail;
       private double cap stress;
       private double pwb moment;
       private double cap force;
//
//
       Throw an error
//
private void error (String msg) throws Exception
{
       throw new Exception (msg);
}
//
//
       Compute results
//
public void computeResults (String mlccmaker, String dielect,
                              String mlccsize, String solderjoint,
                              String soldermat, String loadtype,
                              String capthickStr, String solderpadStr,
                              String solderlengthStr, String solderthickStr,
                              String pwbthicknessStr, String pwbmodStr,
                              String pwbloadStr) throws Exception
//
//
       Check data passed from webpage to applet
//
{
       if (capthickStr.length() == 0)
```

```
error ("The Capacitor Thickness Field Is Empty");
       if (solderpadStr.length() == 0)
               error ("The Solder Pad Width Field Is Empty");
       if (solderlengthStr.length() == 0)
               error ("The Solder Pad length Field Is Empty");
       if (solderthickStr.length() == 0)
               error ("The Solder thickness Field Is Empty");
       if (pwbthicknessStr.length() == 0)
               error ("The PWB Thickness Field Is Empty");
       if (pwbmodStr.length() == 0)
               error ("The PWB Modulus Field Is Empty");
       if (pwbloadStr.length() == 0)
               error ("The PWB Load Field Is Empty");
//
// Convert passed strings to doubles and check for errors
//
// Capacitor Thickness
//
       double capthick = 0;
       try {
               capthick = Double.valueOf(capthickStr).doubleValue();
       } catch (Exception ex) {
               error ("Invalid Capacitor Thickness Value");
        ł
//
// Solder Pad Width
//
       double solderpad = 0;
       try {
               solderpad = Double.valueOf(solderpadStr).doubleValue();
       } catch (Exception ex) {
               error ("Invalid Solder Pad Width Value");
       }
       if (solderpad < 85 || solderpad > 125)
               error ("Solder Pad Width Must Be Between 85 and 125");
//
// Solder Pad Length
//
```

```
double solderlength = 0;
       try {
              solderlength = Double.valueOf(solderlengthStr).doubleValue();
       } catch (Exception ex) {
              error ("Invalid Solder Pad Length Value");
//
// Solder Thickness
//
       double solderthick = 0;
       try {
              solderthick = Double.valueOf(solderthickStr).doubleValue();
       } catch (Exception ex) {
              error ("Invalid Solder Thickness Value");
       }
       if (solderthick < 0.010 \parallel solderthick > 0.254)
              error ("Solder Thickness Must Be Between .010 and 0.254 mm");
//
// PWB Thickness
//
       double pwbthick = 0;
       try {
              pwbthick = Double.valueOf(pwbthicknessStr).doubleValue();
       } catch (Exception ex) {
              error ("Invalid PWB Thickness Value");
       if (pwbthick < 0.7 \parallel pwbthick > 3.4)
              error ("PWB Thickness Must Be Between 0.7 and 3.4 mm");
//
// PWB Modulus
//
       double pwbmod = 0;
       try {
              pwbmod = Double.valueOf(pwbmodStr).doubleValue();
       } catch (Exception ex) {
              error ("Invalid PWB Modulus Value");
       }
       if (pwbmod < 14000 || pwbmod > 22000)
              error ("PWB Modulus Must Be Between 14000 and 22000 MPa");
//
// Get PWB Load Value
//
       double pwb load = 0;
```

```
try {
              pwb load = Double.valueOf(pwbloadStr).doubleValue();
       } catch (Exception ex) {
              error ("Invalid PWB Load Value");
       }
//
//
       Set the size of the capacitor
//
       double cap length = 0;
       double cap width = 0;
       double cap term = 0;
       double cap thick = 0;
       double str x = 0;
       double solder mod = 0;
   if (mlccsize.equals("0201")){
         cap length=0.508;
         cap width=0.254;
         cap thick=0.254;
         cap term=0.15;
    } else if (mlccsize.equals("0402")){
         cap length=1.016;
         cap width=0.508;
         cap thick=0.25;
         cap term=0.15;
    } else if (mlccsize.equals("0603")){
         cap length=1.524;
         cap width=0.762;
         cap thick=0.762;
         cap term=0.35;
    } else if (mlccsize.equals("0805")){
         cap length=2.032;
         cap width=1.27;
         cap thick=capthick;
         cap term=0.5;
    } else if (mlccsize.equals("1206")){
         cap length=3.048;
         cap width=1.524;
         cap thick=capthick;
         cap term=0.5;
```

} else if (mlccsize.equals("1210")){
 cap_length=3.048;
 cap_width=2.54;
 cap_thick=capthick;
 cap_term=0.5;

} else if (mlccsize.equals("1808")){
 cap_length=4.572;
 cap_width=2.032;
 cap_thick=capthick;
 cap_term=0.6;

} else if (mlccsize.equals("1812")){
 cap_length=4.572;
 cap_width=3.048;
 cap_thick=capthick;
 cap_term=0.6;

} else if (mlccsize.equals("1825")){
 cap_length=4.572;
 cap_width=6.35;
 cap_thick=capthick;
 cap_term=0.6;

} else if (mlccsize.equals("2220")){
 cap_length=5.588;
 cap_width=5.08;
 cap_thick=capthick;
 cap_term=0.85;

} else if (mlccsize.equals("2225")){
 cap_length=5.588;
 cap_width=6.35;
 cap_thick=capthick;
 cap_term=0.85;
} else if (mlccsize.equals("2512")){
 cap_length=6.35;
 cap_width=3.048;
 cap_thick=capthick;
 cap_term=0.85;

} else if (mlccsize.equals("3640")){
 cap_length=9.144;
 cap_width=10.16;
 cap thick=capthick;

```
cap term=1.125;
  } else {
         error ("Unsupported MLCC Size Value "+mlccsize+"");
 //
 //
 //
 double pwb I = cap width * Math.pow(pwbthick,3)/12;
 if (loadtype.equals("strain")){
 pwb moment = pwb load * pwbmod * pwb I / (pwbthick/2);
} else if (loadtype.equals("curvature")){
         pwb moment = pwb load * pwbmod * pwb I;
} else if (loadtype.equals("deflection")){
         pwb_moment = pwb_load*12*pwb_I*pwbmod/Math.pow(90,2);
 if (solderjoint.equals("nominal"))
                                      \{ \text{ str } x = 0.7; \}
 else if (solderjoint.equals("starved")) { str x = 0.5; }
 else if (solderjoint.equals("bulbous"))
                                             \{ str x = 1.0; \}
 else { error ("Unsupported Solder Joint Type "+solderjoint+""); }
 double cap I = cap width * Math.pow(cap thick,3)/12;
  cap length=cap length/2;
 if (soldermat.equals("PbSn")) { solder_mod = 27000; }
 else if (soldermat.equals("SnAgCu"))
                                             \{ solder mod = 40000; \}
 else { error ("Unsupported Solder Material "+soldermat+""); }
 double solder lgth = str x * solderlength;
 double solder width = cap width * solderpad/100;
  double solder A = solder lgth * solder width;
 double cap mod = 0;
 //
 if (dielect.equals("Y5V"))
                                       \{ cap mod = 105000; \}
 else if (dielect.equals("X7R"))
                                              \{ cap mod = 110000; \}
                                              \{ cap mod = 120000; \}
 else if (dielect.equals("C0G"))
                                       { cap mod = 337000; }
 else if (dielect.equals("AlO3"))
 else { error ("Unsupported Dielectric Material "+dielect+""); }
 double pwb shear =
  9*((pwbmod/2.6)*(solder width+solderlength)/4)/1.82*1.4*Math.pow(pwbthick,
 0.5);
```

}

```
double solder stiff = 1/(1/pwb shear + 1/(solder A * (solder mod / 2.6) /
solderthick));
double margin stiff = cap term * cap width * (70000 / 2.6) / 0.010;
double pad stiff = solder A * (120000 / 2.6) / 0.035;
double cap stiff = cap thick * cap width * cap mod / cap length;
double combine stiff = 1/(1/\text{solder stiff}+1/\text{pad stiff}+1/\text{cap stiff});
double rot stiff = combine stiff * Math.pow(pwbthick/2,2);
double pwb rot = pwbmod * pwb I / (cap length - cap term/2);
double theta = pwb moment/(pwb rot + rot stiff);
cap force = (pwbthick/2)^* combine stiff * theta;
cap stress = cap force/ (cap width*cap thick)*(3.18*cap thick +
1.2)*Math.pow(1.575/pwbthick,1.2);
double w mod = 0;
double chr str = 0;
double width = 0;
if (mlccmaker.equals("Generic 1 mm")){
       w mod=5.16;
              chr str=100.6;
              width=1.27;}
else if (mlccmaker.equals("Generic 2 mm")){
       w mod=4.87;
              chr str=131.8;
              width=1.524;}
else if (mlccmaker.equals("Syfer")){
              w mod=4.87;
              chr str=131.8;
              width=1.524;}
else if (mlccmaker.equals("TDK")){
       w mod=5.5;
              chr str=134.2;
              width=1.27;}
else if (mlccmaker.equals("muRata")){
              w mod=4.6;
              chr str=100.6;
              width=5.16;}
else
       error ("Unsupported MLCC Manufacturer "+mlccmaker+"");
```

cap_fail=(1-Math.exp(1*cap width/width*Math.pow((cap stress/chr str),w mod)))*100;

}

```
public String getCapFailure ()
{
       if (Double.isNaN(cap_fail))
              return "NaN";
       return failureFmt.format(cap fail);
}
public String getForce ()
{
       if (Double.isNaN(cap_force))
              return "NaN";
       return failureFmt.format(cap_force);
}
public String getStress ()
{
       if (Double.isNaN(cap_stress))
              return "NaN";
       return stressFmt.format(cap stress);
}
public String getMoment ()
ł
       if (Double.isNaN(pwb_moment))
              return "NaN";
       return stressFmt.format(pwb_moment);
}
}
```

10.4 Printed wiring board computations

10.4.1 Element 2, computations

Effective flexural modulus (E_f) is computed as three rotational springs in parallel using the flexural stiffness (EI/L) that is then normalized to just the solder dimensions. The length of the solder joint is assumed to be the length of the device end metallization plus an additional length based upon the fillet shape. This additional length is computed by equation using the variables defined in Figure 2-3 and the solder joint type.

$$L_{eff} = l_{pad} - (t_{sj}) \frac{(t_{sj} + j_f t_c)}{(l_{pad} - l_c)} - l_c$$

Where:

L_{eff} is the new effective length of the solder

 j_c is the joint factor:

0.5 for starved joints0.7 for nominal joints

1.0 for bulbous joints

For the example, this new computed solder length is 0.9 mm and the calculations for the flexural modulus are shown in Figure 10-8.

End metallization

$$W_{1,2,3} = 1.524, A = WL$$
End metallization

$$E_1 = 100 \text{ GPa}$$

$$T_1 = 0.010 \text{ mm}, L_1 = 0.5 \text{ mm}$$
Solder

$$I_1 = \frac{wl^3}{12} = \frac{1.524 \cdot 0.5^3}{12} = 0.0159$$

$$I_2 = \frac{1.524 \cdot 0.9^3}{12} = 0.0926$$

$$I_3 = \frac{1.524 \cdot 1.0^3}{12} = 0.127$$

$$E_f = \frac{T_2}{I_2} \cdot \frac{1}{\frac{T_1}{E_1I_1} + \frac{T_2}{E_2I_2} + \frac{T_2}{E_3I_3}} = 12672 \text{ MPa}$$

Figure 10-8: Effective flexural modulus calculations

The tensile modulus is based upon the area and the thickness of each section. These are added up as springs in parallel and then normalized to the solder dimensions to calculate the effective tensile modulus of the element.

$$E_{t} = \frac{L_{2}}{A_{2}} \cdot \frac{1}{\frac{L_{1}}{E_{1}A_{1}} + \frac{L_{2}}{E_{2}A_{2}} + \frac{L_{2}}{E_{3}A_{3}}} = 13610 \text{ MPa}$$

Equation 10-1: Effective tensile modulus calculations

10.5 Stiffness Method

Portions of the structure will be assumed to behave as beams even though the length to width ratio (aspect ratio) may not be suitable for a beam type approximation. Each beam element has six degrees of freedom as shown in Figure 10-9. Each number corresponds to either a force or displacement.



Figure 10-9: Degrees of freedom for a beam element

The stiffness of the beam to an applied unit displacement is shown in matrix form in Figure 10-10. The formation of this local stiffness matrix can be found in numerous references [74].

$$k' = \begin{bmatrix} \frac{AE}{L} & 0 & 0 & -\frac{AE}{L} & 0 & 0 \\ 0 & \frac{12EI}{L^{2}(1+4r)} & \frac{6EI}{L^{2}(1+4r)} & 0 & \frac{12EI}{L^{2}(1+4r)} & \frac{6EI}{L^{2}(1+4r)} \\ 0 & \frac{6EI}{L^{2}(1+4r)} & \frac{4EI}{L}(\frac{1+r}{1+4r}) & 0 & \frac{12EI}{L^{2}(1+4r)} & \frac{2EI}{L}(\frac{1-2r}{1+4r}) \\ -\frac{AE}{L} & 0 & 0 & \frac{AE}{L} & 0 & 0 \\ 0 & -\frac{12EI}{L^{2}(1+4r)} & -\frac{6EI}{L^{2}(1+4r)} & 0 & \frac{12EI}{L^{2}(1+4r)} & -\frac{6EI}{L^{2}(1+4r)} \\ 0 & \frac{6EI}{L^{2}(1+4r)} & \frac{2EI}{L}(\frac{1-2r}{1+4r}) & 0 & -\frac{6EI}{L^{2}(1+4r)} & \frac{4EI}{L}(\frac{1+r}{1+4r}) \end{bmatrix} \\ A_{S} = \frac{A}{K} : \text{Shear area} \\ r = \frac{3EI}{GA_{S}L^{2}} & K = 1.2 : \text{Rectangular cross section} \\ F = Modulus of Elasticity \\ G = \frac{E}{2(1+\nu)} & I = \text{Moment of Inertia} \\ r = \text{Dimension of the section} \end{bmatrix}$$

I = Moment of Inertia

 $\nu =$ Poisson's ratio

L = Length of the beam

Figure 10-10: Beam stiffness matrix with shear compliance [74]

The overall structure has three elements and four nodes and, as shown in Figure 10-11, has 12 degrees of freedom. The degrees of freedom are numbered starting with the unconstrained degrees of freedom first and continuing counter clockwise to the constrained degrees of freedom. The load and displacement matrices correspond to the boundary and loading conditions shown in Figure 2-4. These form the global displacement and the global load matrices as shown in Figure 10-12.


Figure 10-11: Degree of freedom numbering

Global Displacement Matrix

Global Load Matrix

D_1	0
D_2	0
D_3	М
D_4	0
D_5	0
D_{6}	0
0	0
D_8	ů O
0	0
0	0
0	0
0	0
0	0

Figure 10-12: Global load and displacement matrices

The local force matrix for each element is transformed from the local coordinates of the beam to the global coordinates of the structure. This is to align the local coordinates to those of the global structure and is done by multiplying the local matrix by a transformation matrix. The transformation matrix relates the local member to the global structure and can be expressed in geometric terms and in matrix form as shown in Figure 10-13, where θ_X is the angle from the global structure x axis to the element and θ_Y is the angle from the global structure y axis to the element.

	$\cos \theta_{X}$	$\cos \theta_{Y}$	0	0	0	0
	$-\cos\theta_{y}$	$\cos\theta_{X}$	0	0	0	0
T _	0	0	1	0	0	0
1 =	0	0	0	$\cos \theta_{X}$	$\cos\theta_{Y}$	0
	0	0	0	$-\cos\theta_{Y}$	$\cos\theta_{X}$	0
	0	0	0	0	0	1

Figure 10-13: Displacement transformation matrix

This transformation matrix also relates the global stiffness matrix to the local stiffness matrix through the following relationship $[k] = [T]^T [k'][T]$ where k' is the local member stiffness matrix, k is the global stiffness member matrix and T is the transformation matrix. The global stiffness matrix can then be assembled. The boundary conditions are then be applied to the global stiffness matrix to reduce the matrix.

The structure is assumed to be symmetric, and is discretized into three elements as shown in Table 38. Element 1 is the body of the device, element 2 is a combination of the solder, bond-pad, and end-metallization, and element 3 is the printed wiring board. The material properties used are shown in Table 5. There are four degrees of freedom for the symmetric structure of a LCC/LCR mounted to a printed wiring board.

Table 38: Degrees of freedom, and node/element numbering



The structure has the nodes labeled as shown in Table 38 and the load (M) at joint 3 is representative of the moment applied to structure due to printed wiring board bending. Using the degrees of freedom numbering shown in Table 38, the global stiffness matrix for element 1 is shown in Figure 10-14.

$$k_{1} = \begin{bmatrix} \frac{A_{1}E_{1}}{L_{1}} & 0 & 0 & -\frac{A_{1}E_{1}}{L_{1}} & 0 & 0 \\ 0 & \frac{12E_{1}I_{1}}{L_{1}^{3}(1+4r_{1})} & \frac{6E_{1}I_{1}}{L_{1}^{2}(1+4r_{1})} & 0 & \frac{-12E_{1}I_{1}}{L_{1}^{3}(1+4r_{1})} & \frac{6E_{1}I_{1}}{L^{2}(1+4r_{1})} \\ 0 & \frac{6E_{1}I_{1}}{L_{1}^{2}(1+4r_{1})} & \frac{4E_{1}I_{1}}{L_{1}}\left(\frac{1+r_{1}}{1+4r_{1}}\right) & 0 & \frac{-6E_{1}I_{1}}{L^{2}(1+4r_{1})} & \frac{2E_{1}I_{1}}{L_{1}}\left(\frac{1-2r_{1}}{1+4r_{1}}\right) \\ \frac{-A_{1}E_{1}}{L_{1}} & 0 & 0 & \frac{A_{1}E_{1}}{L_{1}} & 0 & 0 \\ 0 & \frac{-12EI}{L_{1}^{3}(1+4r_{1})} & \frac{-6E_{1}I_{1}}{L^{2}(1+4r_{1})} & 0 & \frac{12E_{1}I_{1}}{L_{1}^{3}(1+4r_{1})} & \frac{-6E_{1}I_{1}}{L^{2}(1+4r_{1})} \\ 0 & \frac{6E_{1}I_{1}}{L_{1}^{2}(1+4r_{1})} & \frac{2E_{1}I_{1}}{L^{2}(1+4r_{1})} & 0 & \frac{-6E_{1}I_{1}}{L^{2}(1+4r_{1})} \\ \end{bmatrix}$$

Figure 10-14: Global stiffness matrix for element 1

The local stiffness matrix for element 2 must be rotated -90 degrees to align with the global coordinates. The resulting global stiffness matrix for element 2 is shown in Figure 10-15. The elastic modulus for element 2 is a combination of the materials that comprise the solder, bond pad, and end-metallization. The flexural modulus and tensile modulus for element 2 are computed as a set of three springs in series. The detailed computations are provided in Appendix 10.4.1. The local stiffness matrix for element 3 is transformed to align with the global coordinates. The resulting global stiffness matrix for element 3 is shown in Figure 10-16.

$$k_{2} = \begin{bmatrix} \frac{12E_{2}I_{2}}{L_{2}^{3}(1+4r_{2})} & 0 & \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{-12E_{2}I_{2}}{L_{2}^{3}(1+4r_{2})} & 0 & \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} \\ 0 & \frac{A_{2}E_{2}}{L_{2}} & 0 & 0 & \frac{-A_{2}E_{2}}{L_{2}} & 0 \\ \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{4E_{2}I_{2}}{L_{2}}\left(\frac{1+r_{2}}{1+4r_{2}}\right) & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{2E_{2}I_{2}}{L_{2}}\left(\frac{1-2r_{2}}{1+4r_{2}}\right) \\ \frac{-12E_{2}I_{2}}{L_{2}^{3}(1+4r_{2})} & 0 & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{12E_{2}I_{2}}{L_{2}^{3}(1+4r_{2})} & 0 & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} \\ 0 & \frac{-A_{2}E_{2}}{L_{2}} & 0 & 0 & \frac{A_{2}E_{2}}{L_{2}^{2}(1+4r_{2})} \\ 0 & \frac{-A_{2}E_{2}}{L_{2}} & 0 & 0 & \frac{A_{2}E_{2}}{L_{2}} & 0 \\ \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{2E_{2}I_{2}}{L_{2}}\left(\frac{1-2r_{2}}{1+4r_{2}}\right) & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{4E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} \end{bmatrix}$$

Figure 10-15: Global stiffness matrix for element 2

$$k_{3} = \begin{bmatrix} \frac{A_{3}E_{3}}{L_{3}} & 0 & 0 & \frac{-A_{3}E_{3}}{L_{3}} & 0 & 0 \\ 0 & \frac{12E_{3}I_{3}}{L_{3}^{3}(1+4r_{3})} & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & 0 & \frac{-12E_{3}I_{3}}{L_{3}^{3}(1+4r_{3})} & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{4E_{3}I_{3}}{L_{3}}\left(\frac{1+r_{3}}{1+4r_{3}}\right) & 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{2E_{3}I_{3}}{L_{3}}\left(\frac{1-2r_{3}}{1+4r_{3}}\right) \\ \frac{-A_{3}E_{3}}{L_{3}} & 0 & 0 & \frac{A_{3}E_{3}}{L_{3}} & 0 & 0 \\ 0 & \frac{-12E_{3}I_{3}}{L_{3}^{3}(1+4r_{3})} & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & 0 & \frac{12E_{3}I_{3}}{L_{3}^{3}(1+4r_{3})} & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{2E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{2E_{3}I_{3}}{L_{3}}\left(\frac{1-2r_{3}}{1+4r_{3}}\right) & 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{2E_{3}I_{3}}{L_{3}}\left(\frac{1-2r_{3}}{1+4r_{3}}\right) & 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{-6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{2E_{3}I_{3}}{L_{3}}\left(\frac{1-2r_{3}}{1+4r_{3}}\right) & 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{4E_{3}I_{3}}{L_{3}}\left(\frac{1+r_{3}}{1+4r_{3}}\right) \\ 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{6E_{3}I_{3}}{L_{3}^{2}(1+4r$$

Figure 10-16: Global stiffness matrix for element 3

These global element matrices can now be assembled into the assembly global stiffness matrix. The global matrix, which is a 12×12 matrix, can be reduced to a 7×7 matrix by applying the boundary conditions. The reduced matrix is shown in Figure 10-17.

$$K = \begin{bmatrix} \frac{AE_{1}}{L_{1}} + \frac{12E_{2}I_{2}}{L_{2}^{3}(1+4r_{2})} & 0 & \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{-12E_{2}I_{2}}{L_{2}^{3}(1+4r_{2})} & 0 & \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 \\ 0 & \frac{12E_{1}I_{1}}{L_{1}^{3}(1+4r_{1})} + \frac{A_{2}E_{2}}{L_{2}} & \frac{-6E_{1}I_{1}}{L_{1}^{2}(1+4r_{1})} & 0 & \frac{-A_{2}E_{2}}{L_{2}} & 0 & 0 \\ \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{-6E_{1}I_{1}}{L_{1}^{2}(1+4r_{1})} & \frac{4E_{1}I_{1}(\frac{1+r_{1}}{1+4r_{1}}) + \frac{4E_{2}I_{2}(\frac{1+r_{2}}{1+4r_{2})}}{L_{2}^{2}(1+4r_{2})} & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{2E_{2}I_{2}(\frac{1-2r_{2}}{1+4r_{2})} & 0 \\ \frac{-12E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{12E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} + \frac{A_{2}E_{2}}{L_{2}^{2}(1+4r_{2})} & 0 \\ \frac{-12E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{12E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{-6E_{2}I_{3}}{L_{2}^{2}(1+4r_{3})} & \frac{-6E_{2}I_{3}}{L_{2}^{2}(1+4r_{3})} & \frac{-12E_{2}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ 0 & \frac{-A_{2}E_{2}}{L_{2}} & 0 & 0 & \frac{A_{2}E_{2}}{L_{2}^{2}(1+4r_{2})} & \frac{-6E_{2}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{-12E_{2}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{2E_{2}I_{2}(\frac{1-2r_{2}}{1+4r_{2})} & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{3})} & \frac{-6E_{2}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{-12E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ \frac{-6E_{2}I_{2}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{2E_{2}I_{2}(\frac{1-2r_{2}}{1+4r_{2}}) & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{3})} & \frac{-6E_{2}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{-12E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} \\ \frac{-6E_{2}I_{2}}}{L_{2}^{2}(1+4r_{2})} & 0 & \frac{2E_{2}I_{2}(\frac{1-2r_{2}}{1+4r_{2}}) & \frac{6E_{2}I_{2}}{L_{2}^{2}(1+4r_{3})} & \frac{4E_{2}I_{2}(\frac{1+r_{2}}{1+4r_{3}}) + \frac{4E_{3}I_{3}(\frac{1+r_{3}}{1+4r_{3}})} \\ \frac{-6E_{2}I_{2}}}{L_{2}^{2}(1+4r_{2})} & 0 & 0 & 0 & 0 & \frac{12E_{3}I_{3}}{L_{3}^{2}(1+4r_{3})} & \frac{4E_{3}I_{3}(\frac{1+r_{3}}{1+r_{3}}) + \frac{4E_{3}I_{3}(\frac{1+r_{3}}{1+r_{3}})} \\ \frac{-6E_{2}I_{2}}}{L_{2}^{2}(1+4r_{2})} & \frac{-6E_{2}I_{3}}{L_{2}^{2}(1+4r_{3})} & \frac{4E_{2}I_{3}(\frac{1+r_{3}}{1+r_{3}})} & \frac{4E_{3}I_{3$$

Figure 10-17: Reduced global stiffness matrix

The displacements of the structure can now be determined by solving Q = K*D. The reaction forces can then be determined multiplying the partitioned global stiffness matrix by the displacements.

Global Displacement	Global Load			
Matrix [D]	Matrix [Q]			
$\begin{bmatrix} D_1 \\ 0 \\ 0 \\ D_4 \\ D_5 \\ D_6 \\ D_7 \\ D_8 \end{bmatrix}$	$\begin{bmatrix} 0\\0\\0\\0\\0\\0\\M\\0\\0\\0\end{bmatrix}$			
$\left \begin{array}{c} D_{9} \\ 0 \end{array} \right $				
	0			

Figure 10-18: Global load and displacement matrices

The values of interest are the loads applied to the solder and the component. The matrix computations were conducted with Microsoft Excel. The loads are calculated by transforming the global displacements back to the local displacements for the component element. The local stiffness matrix is then multiplied by the local displacements with the result being the loads applied to the component. These loads are converted to the stresses in a rectangular body as shown in Figure 10-19, with the equations given in Table 39.



Figure 10-19: Critical stresses on a rectangular cross section [74]

Table 39: Equations for the critical stresses on a rectangular cross section [74	4]
--	----	---	---

Point	Normal stress o	Shear stress τ
1	$\frac{N}{wl} - \frac{6M_{b}}{wl^{2}} + \frac{6M_{t}}{w^{2}l}$	0
2	$\frac{N}{wl} - \frac{6M_b}{wl^2} - \frac{6M_t}{w^2l}$	0
3	$\frac{N}{wl} + \frac{6M_{b}}{wl^{2}} - \frac{6M_{t}}{w^{2}l}$	0
4	$\frac{N}{wl} + \frac{6M_{\delta}}{wl^2} + \frac{6M_{t}}{w^2l}$	0
5	$\frac{N}{wl} - \frac{6 M_b}{wl^2}$	$\frac{3Q}{2wl} + \frac{kT}{wl^2}$
6	$\frac{N}{wl} + \frac{6M_{b}}{wl^{2}}$	$\frac{3Q}{2wl} - \frac{kT}{wl^2}$
7	$\frac{N}{wl} + \frac{6M_{t}}{w^{2}l}$	$\frac{3V}{2wl} - \frac{skT}{wl^2}$
8	$\frac{N}{wl} - \frac{6M_t}{w^2l}$	$\frac{3V}{2wl} + \frac{skT}{wl^2}$

The maximum stresses will be generated at point 5 with the given loads N and M_b . This tensile stress is used to conduct a rapid assessment of the probability of capacitor failure for a given printed wiring surface strain, curvature or applied moment.

10.6 Probability of failure comparison between PbSn and SnAgCu

🖉 Capacitor Cracking Calculator (v2.0) -	Microsoft Internet Explorer		🙆 Capacitor	Cracking Calculator (v2.0) -	Microsoft Internet Explore	er	
File Edit View Favorites Tools H	elp	-	File Edit	View Favorites Tools H	elp		
← Back ▼ → ▼ 🙆 😰 🖓 🥘 Search 👔	Favorites 🛞 Media 🧭 🛃 🚽 🎒 🖬 👻 🗐		der Back 👻 =	🕨 🛪 🙆 🔂 🖓 🖓 Search 👔	Favorites 🛞 Media 🎯 🖪	- 4 - 5	
Address D:\CapCrack\index.html	▼ 2 ² 6 ² 60	Links » 🐔 👻	Address 🧧	D:\CapCrack\index.html		▼ ∂Go	Links » 📆
Capacito Probab; Due To Pri	r Cracking Calculator dity of MLCC Cracking nted Wiring Board Bending Version 2.0	<u>^</u>		Capacitor Probabi Due To Prin	r Cracking Calculato lity of MLCC Cracking nted Wiring Board Bendin ^{Version 2.0}	g	-
This program calculates the probability of cr typical values for each entry, clicking on t corresponding results. This allows the user to capacitor is assumed to be placed on the PWB	acking an MLCC during PWB bending. Initially the for he Compute button at the bottom of the form will become familiar with the routine and see some typical at the point of greatest deflection.	rm contains display the results. The	This program typical valic correspond capacitor is	am calculates the probability of cra ues for each entry, clicking on th ing results. This allows the user to assumed to be placed on the PWB	cking an MLCC during PWB b ne Compute button at the bot become familiar with the routine at the point of greatest deflection	ending. Initially the fo tom of the form will and see some typical on.	m contains display the results. The
Reset The Form:	Reset			Reset The Form:	Reset		
MLCC Manufacturer:				MLCC Manufacturer:	TDK		
Dielectric Type:	X7R 💌			Dielectric Type:	X7R 💌		
MLCC Size:	1206 Thickness: 1.0 [mm]			MLCC Size:	1206 💌 Thickness: 1.0	[mm]	
Solder Fillet Shape:	nominal 💌			Solder Fillet Shape:	nominal 💌		
Solder Material	PbSn 💌			Solder Material:	SnAgCu 💌		
Solder Pad Width:	100 [% of chip width (85-125)]			Solder Pad Width:	100 [% of chip width (85-	125)]	
Solder Pad Length:	1.0 [mm]			Solder Pad Length:	1.0 [mm]		
Solder Thickness:	0.035 [mm], Typically between 0.0254 and 0.127			Solder Thickness:	0.035 [mm], Typically betw	reen 0.0254 and 0.127	
PWB Thickness:	1.6 [mm]			PWB Thickness:	1.6 [mm]		
PWB Modulus:	17000 [MPa]			PWB Modulus:	17000 [MPa]		
Applied PWB :	0.002 strain [mm/mm. 1/mm. mm]			Applied PWB :	0.002 strain V [mm	/mm 1/mm mm]	
Compute Results:	Compute			Compute Results:	Compute	·····,	
Capacitor Stress:	066.41748 [MPa]			Capacitor Stress:	081.63912 [MPa]		
Board Moment:	022.10816 [N.mm]			Board Moment:	022.10816 [N.mm]		
Probability of Capacitor Failure:	002.47550 %			Probability of Capacitor Failure:	007.50171 %		
Copyright © 2004	by <u>Nathan Elattan</u> , All Rights Reserved			Copyright © 2004	by <u>Nathan Blattan</u> , All Rights Reser	wed	
Applet started.		mputer	Applet start	ed.		My Cor	nputer

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